

Developing a New State of the Art EUV Mask Imaging Research Tool at Berkeley

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Center for X-Ray Optics
Lawrence Berkeley National Laboratory

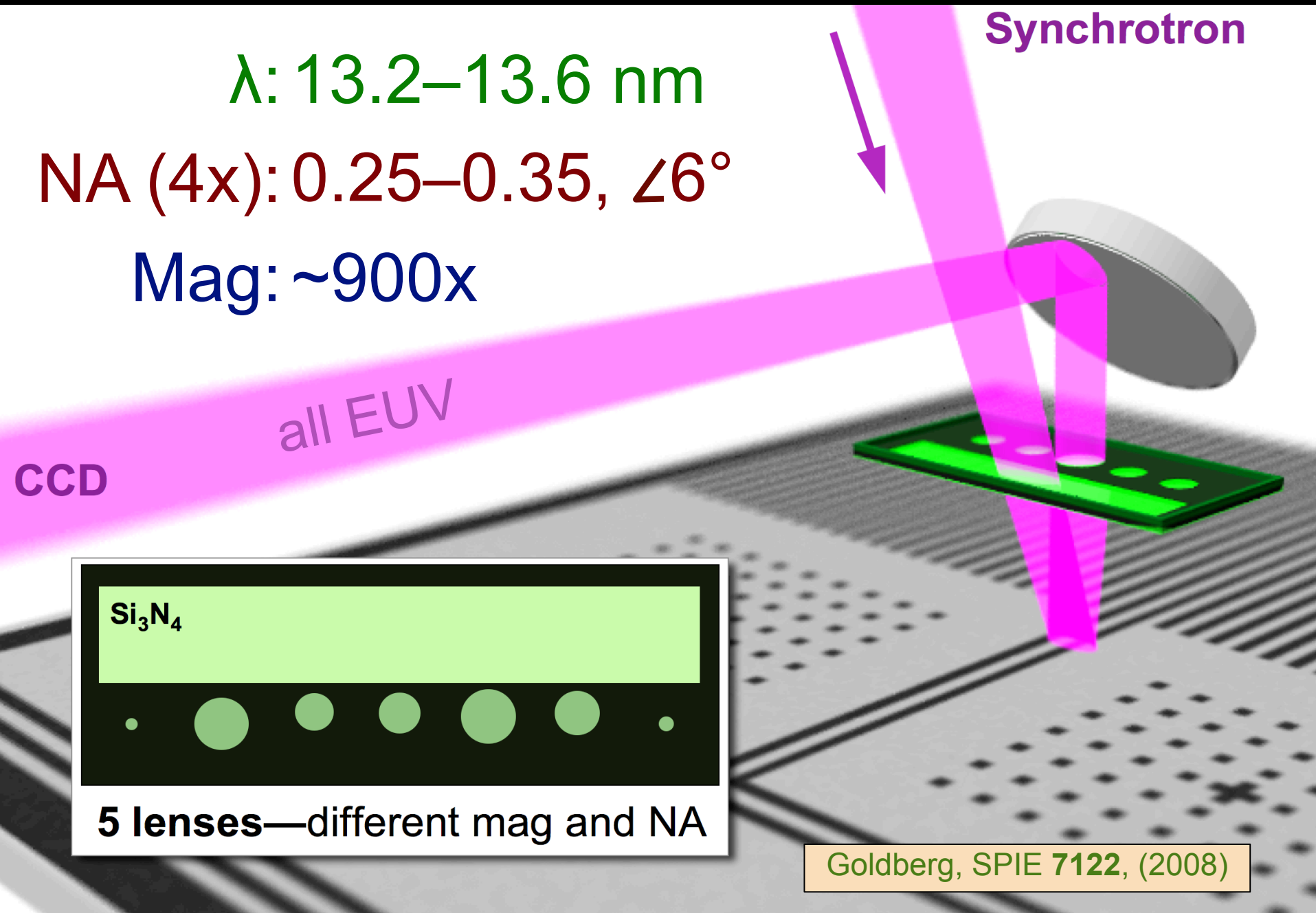


The SEMATECH Berkeley Actinic Inspection Tool (AIT)

λ : 13.2–13.6 nm

NA (4x): 0.25–0.35, $\angle 6^\circ$

Mag: ~900x



Synchrotron

all EUV

CCD

Si_3N_4

5 lenses—different mag and NA

Goldberg, SPIE 7122, (2008)

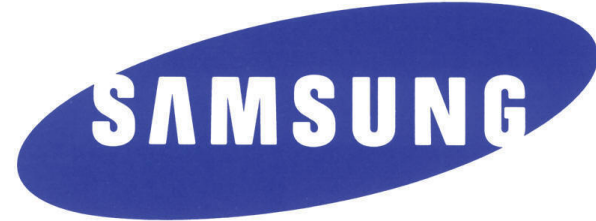
Primary AIT users in 2010/11



CNSE
SUNY Albany



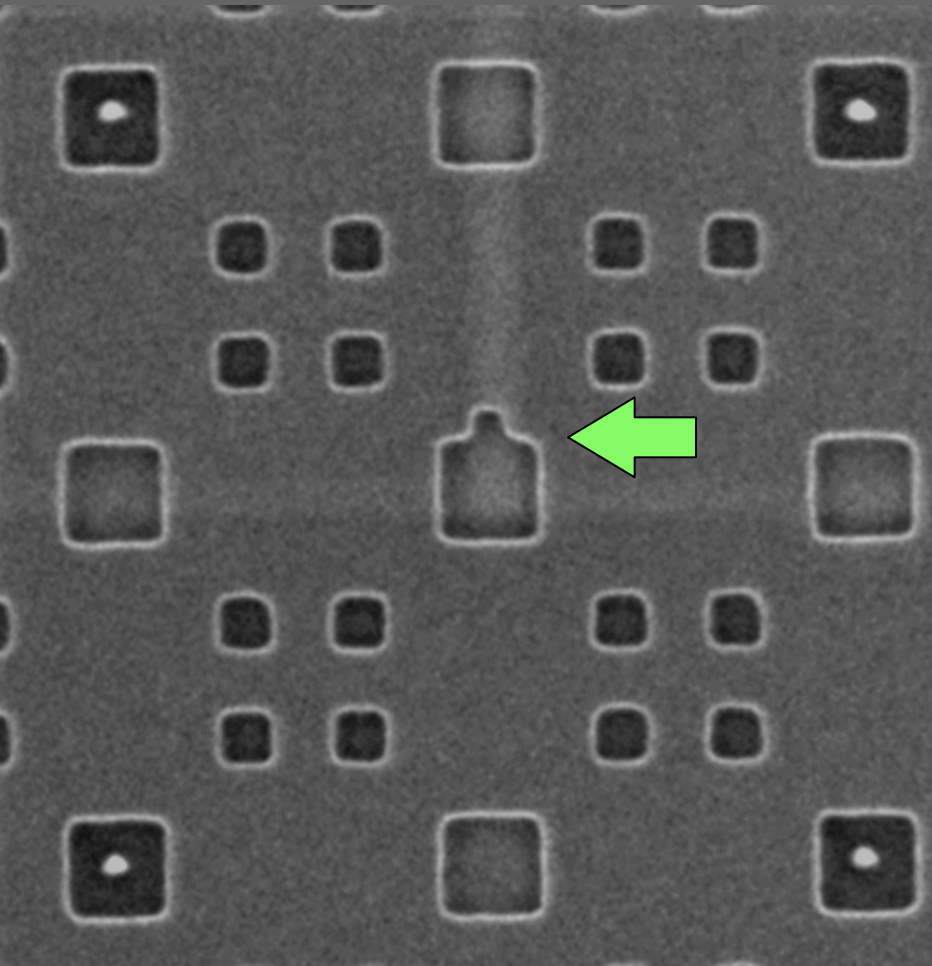
GLOBALFOUNDRIES



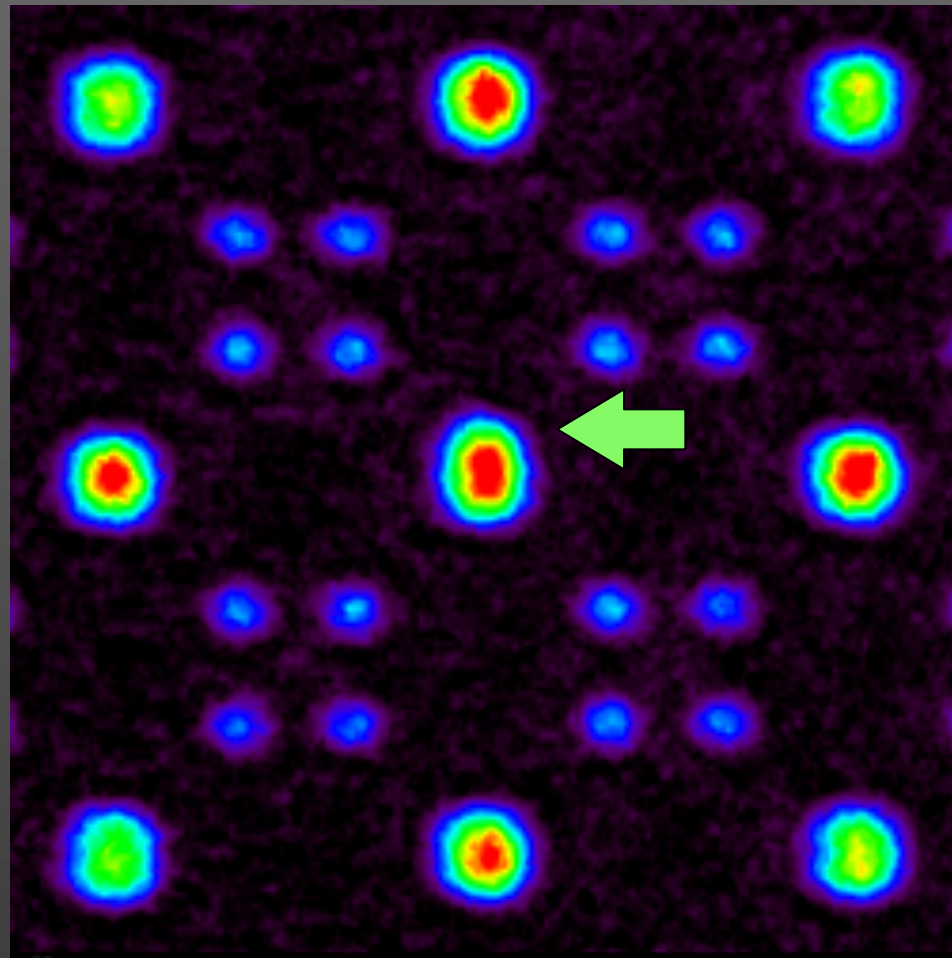
THE CENTER FOR X-RAY OPTICS



IBM Programmed Pattern Defects



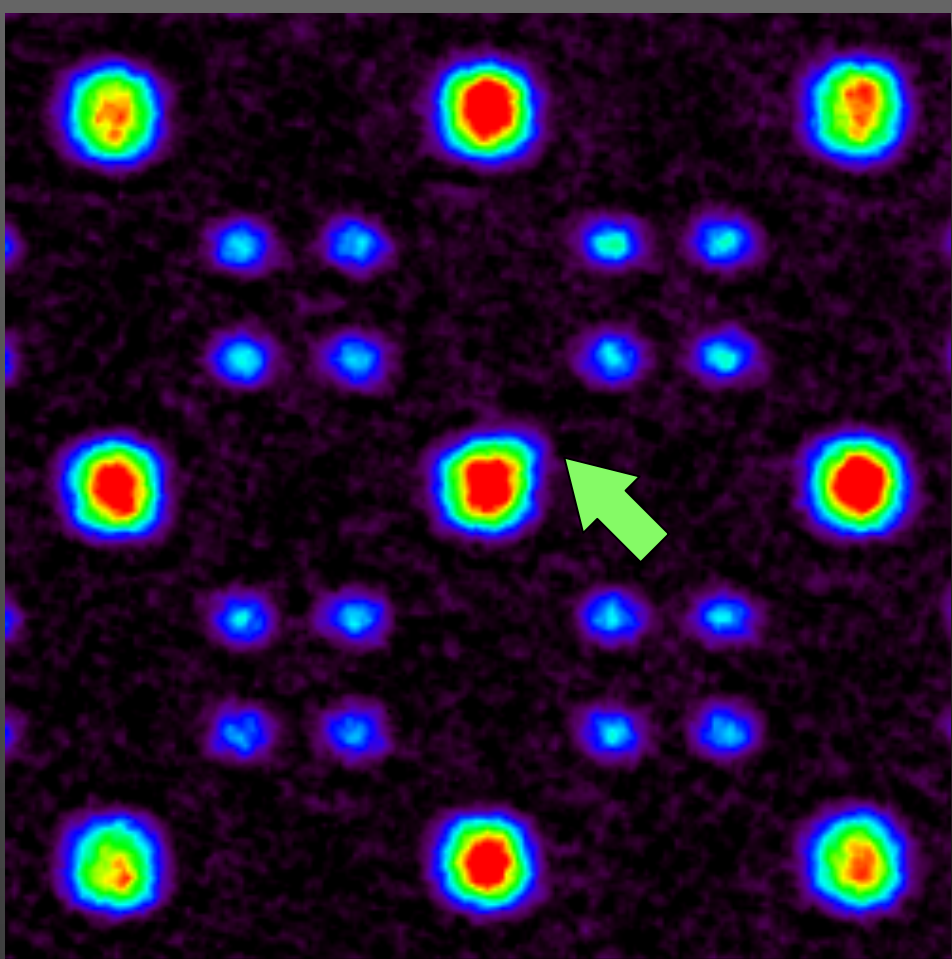
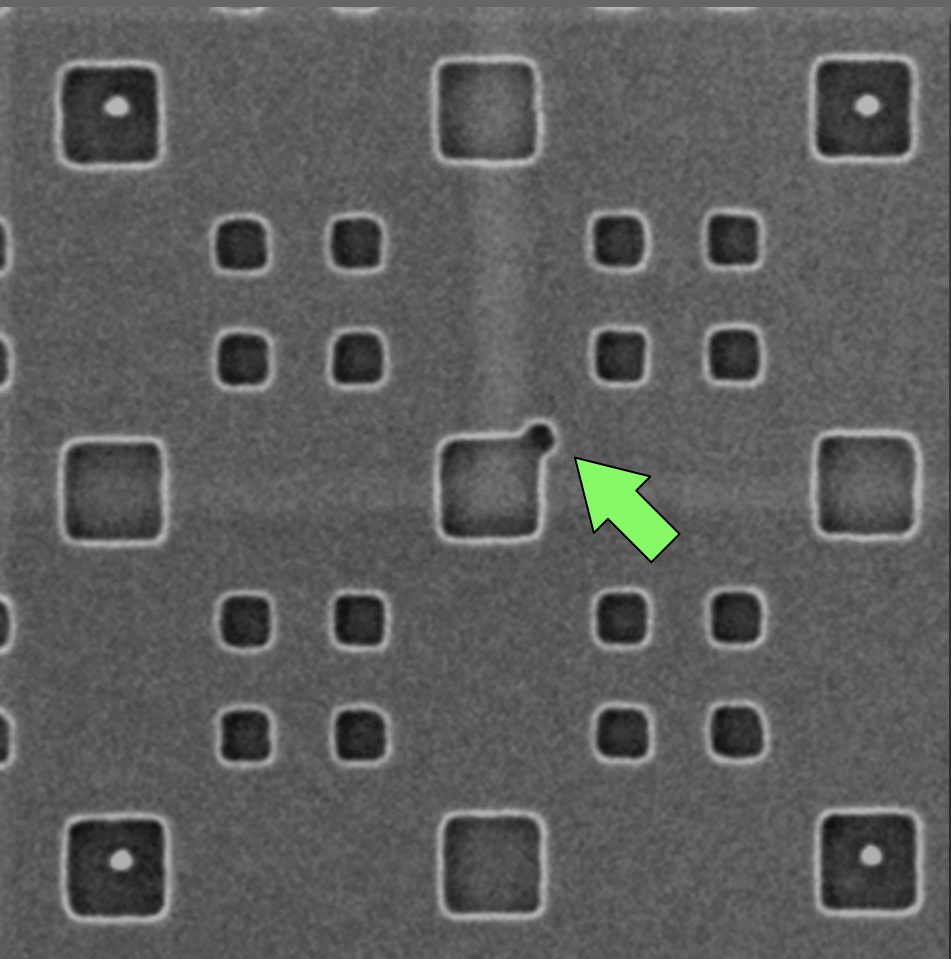
SEM



AIT (EUV)

— 500 nm

IBM Programmed Pattern Defects

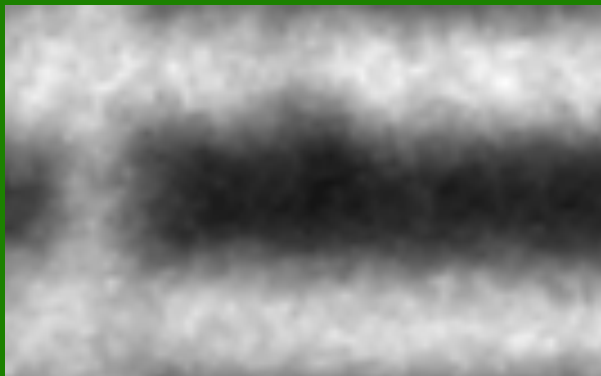


SEM

AIT (EUV)

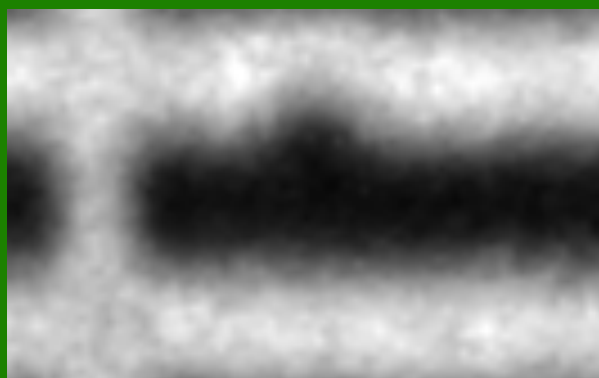
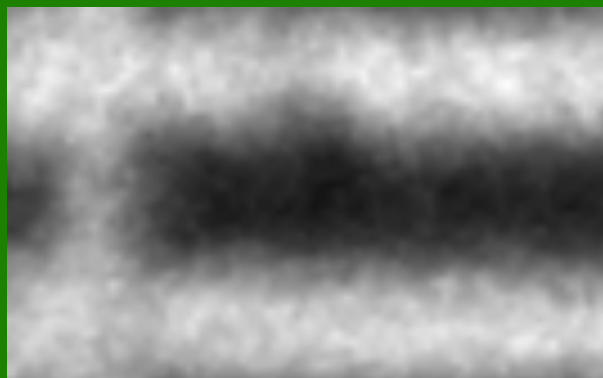
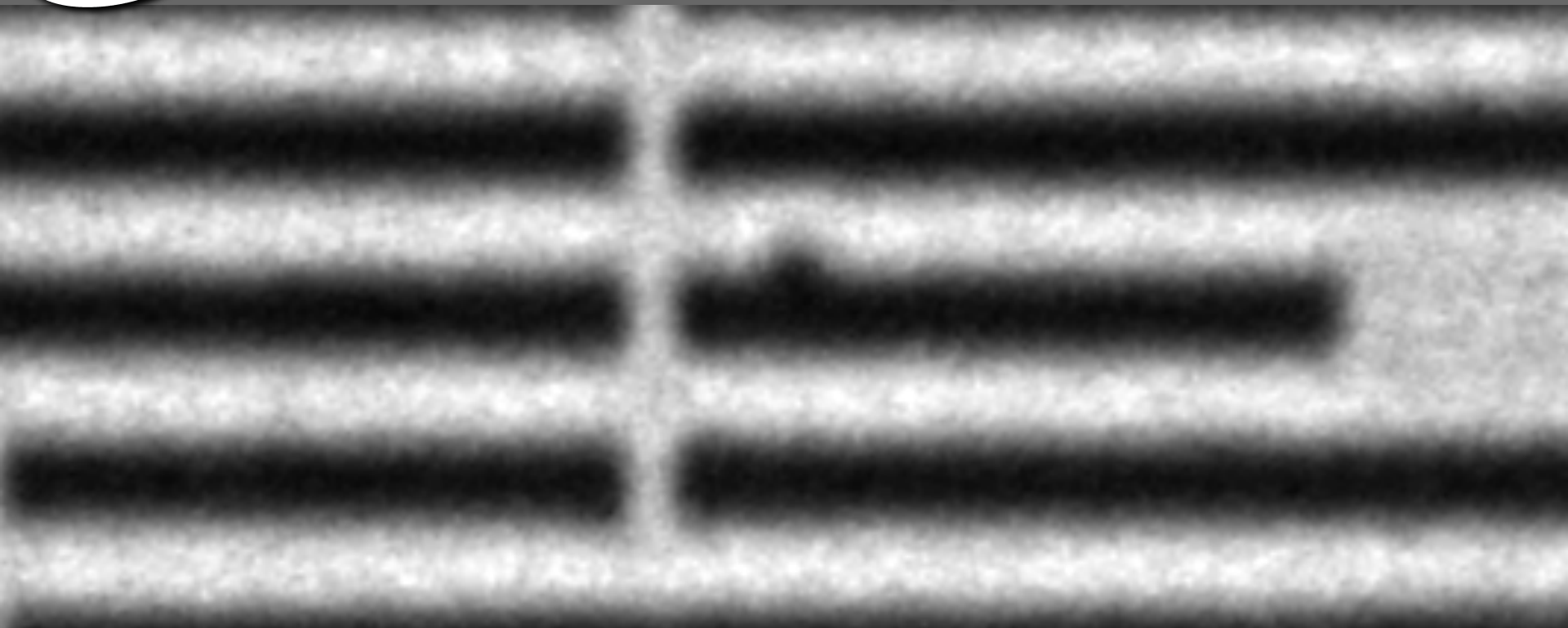
— 500 nm

intel Native Pattern **Amplitude** Defect



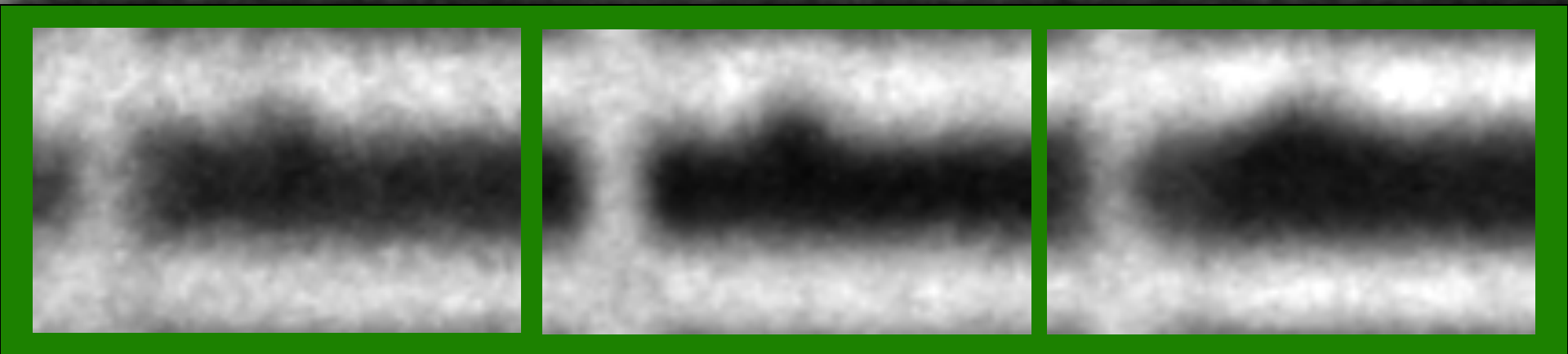
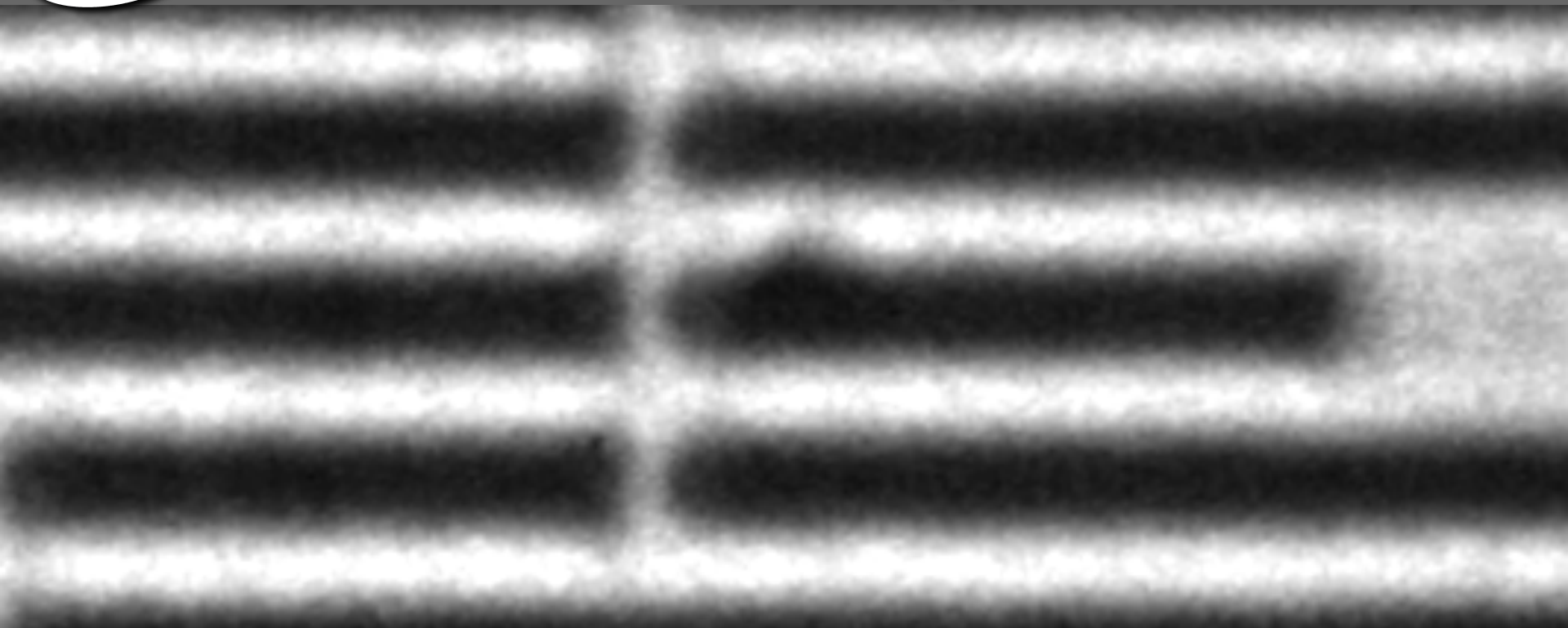


Native Pattern **Amplitude** Defect





Native Pattern **Amplitude** Defect

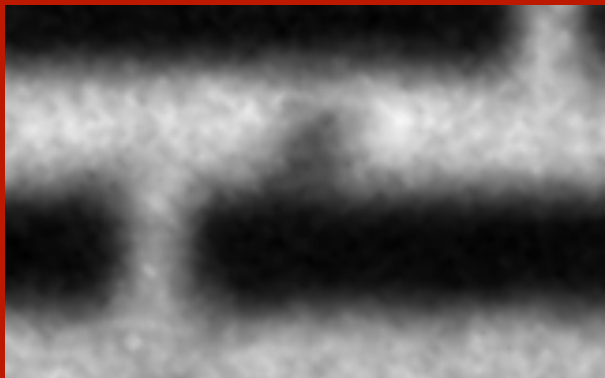
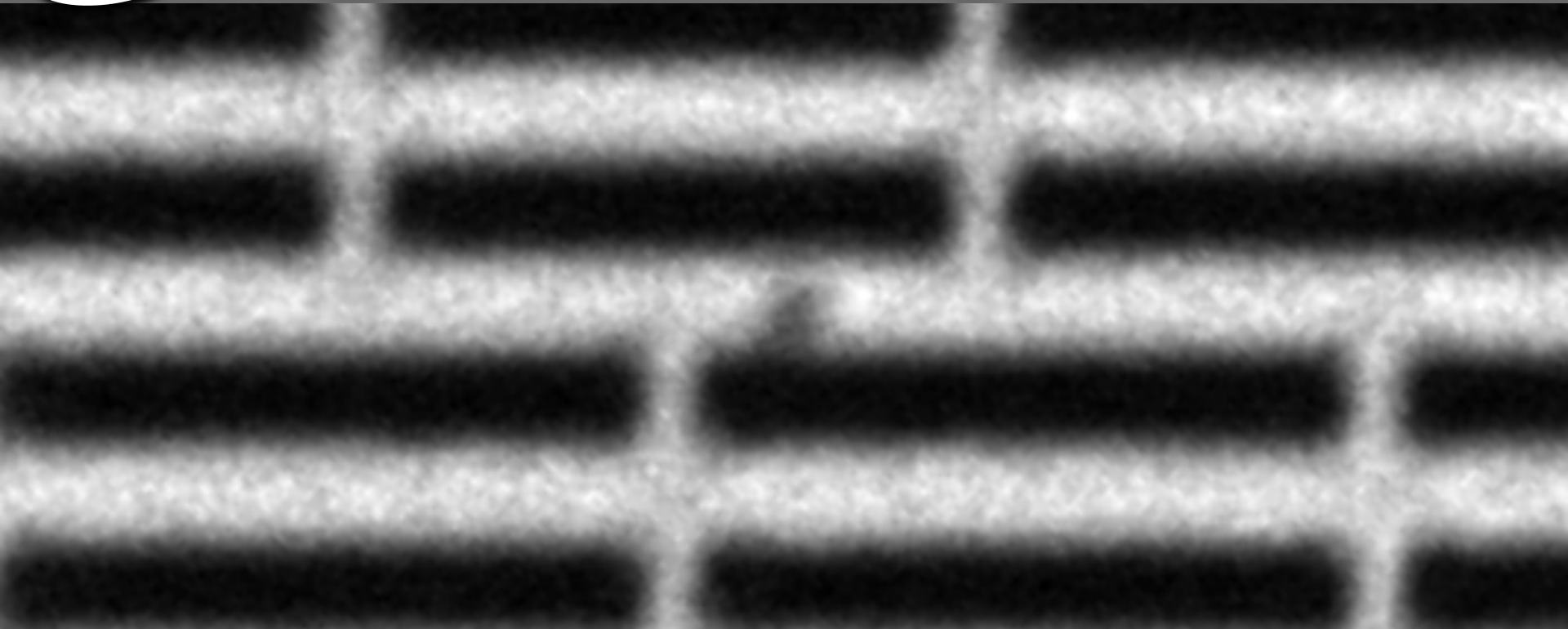


Mask: IMO182140 / Magana, *unpublished 2010*

 **500 nm**

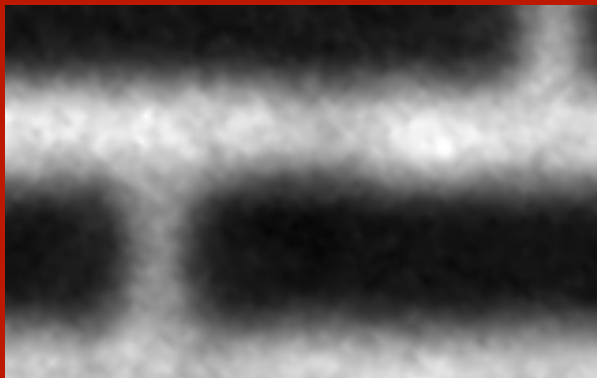
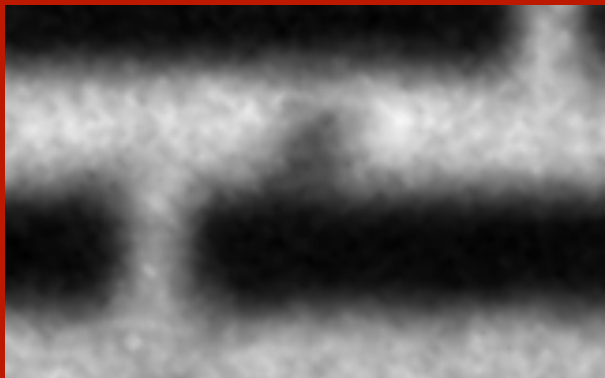
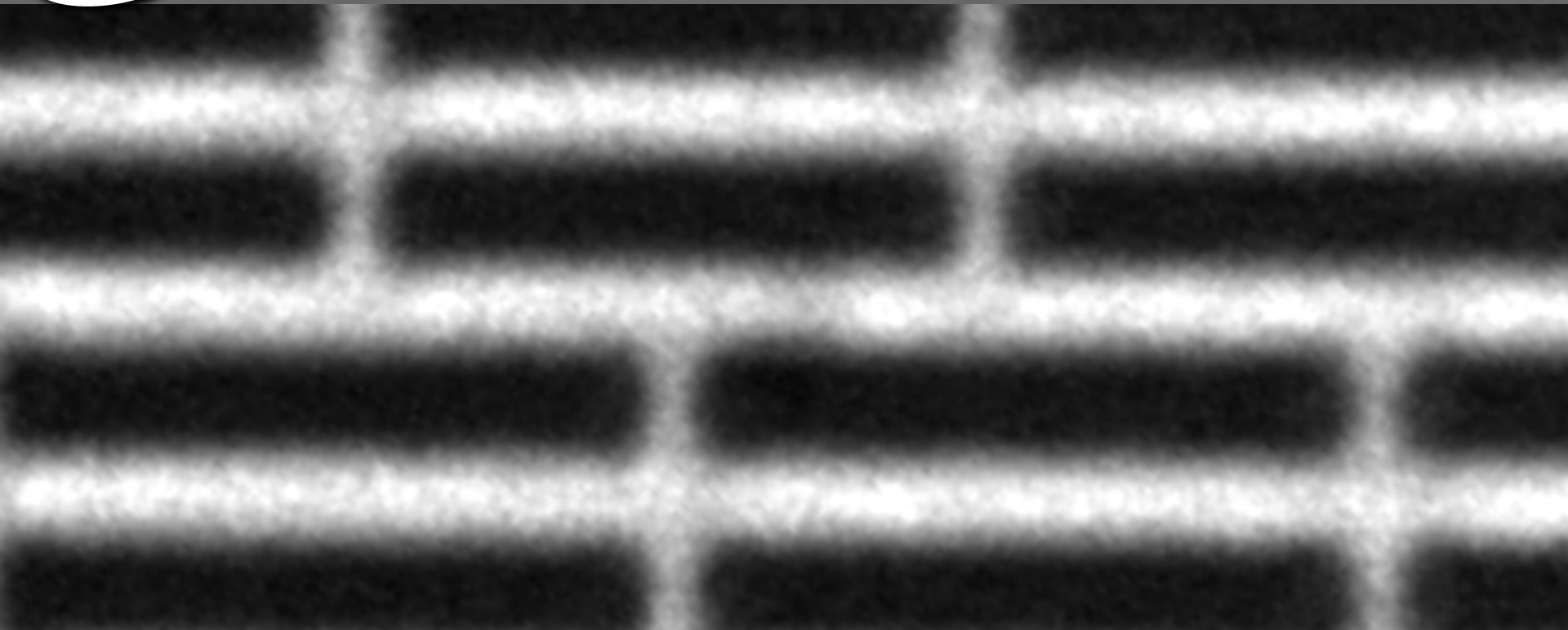


Native Pattern **Phase** Defect



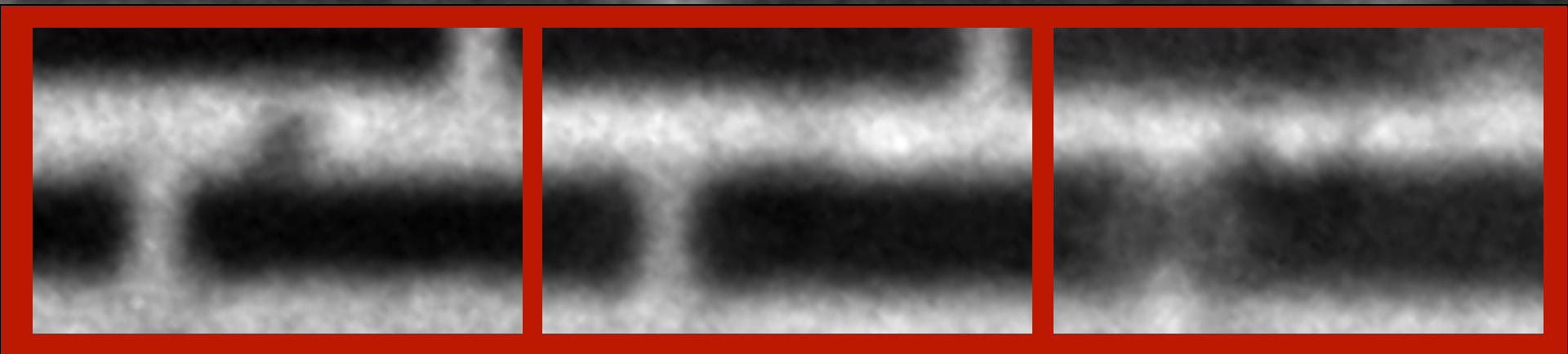
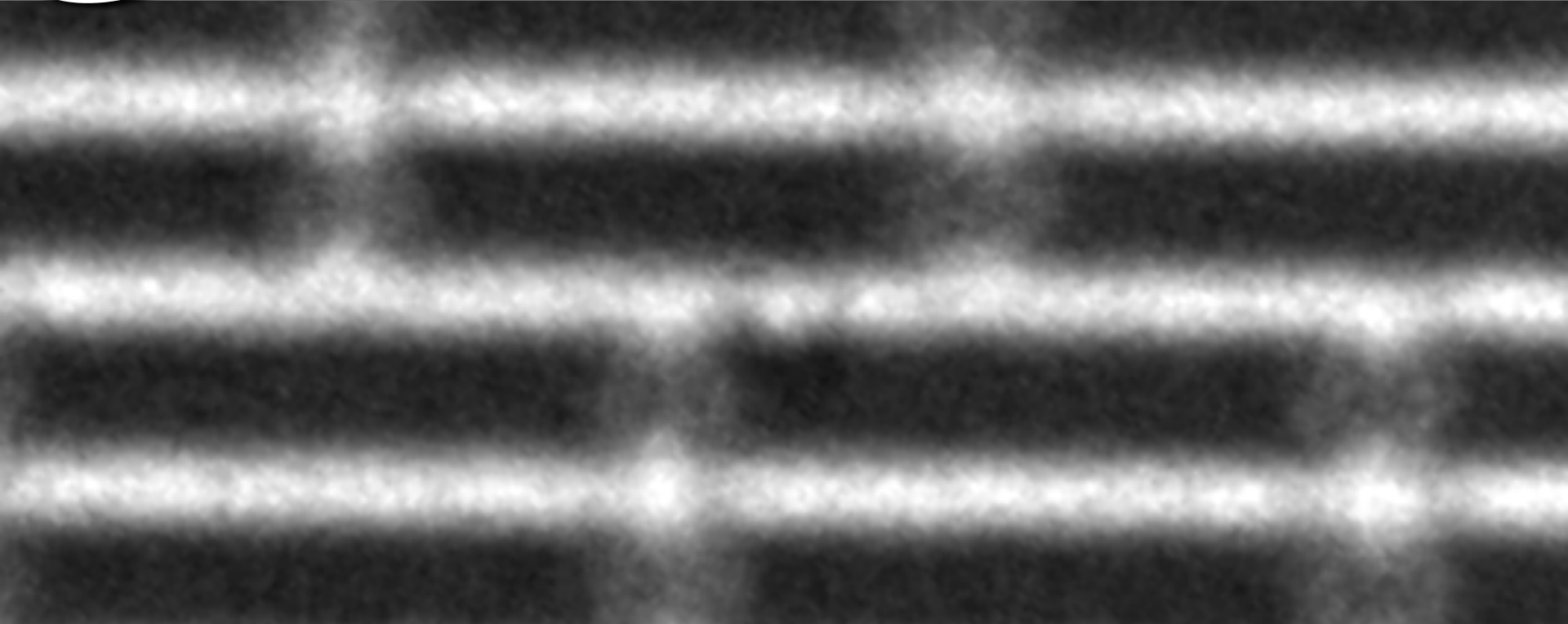


Native Pattern **Phase** Defect





Native Pattern **Phase** Defect



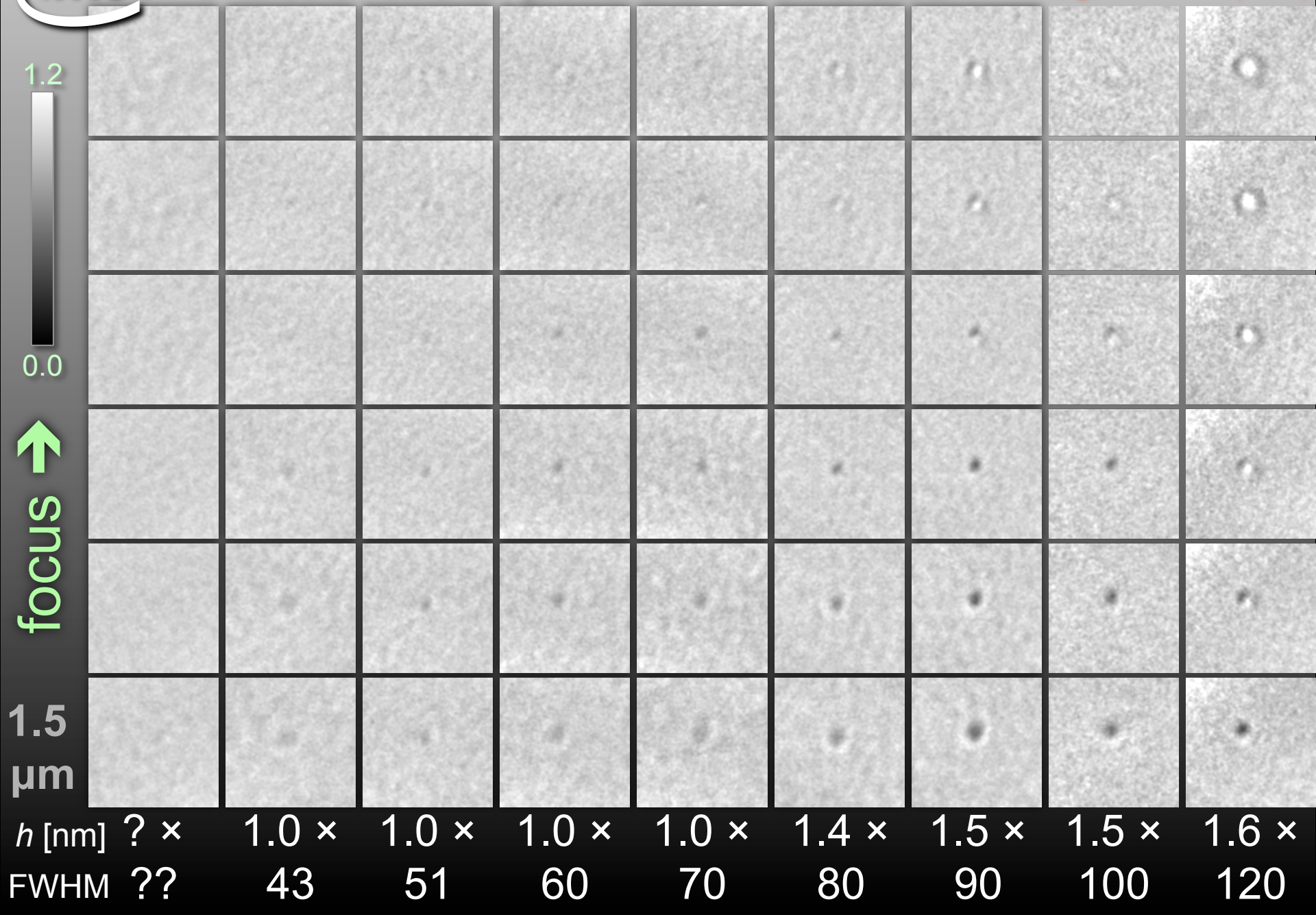
Mask: IMO182140 / Magana, *unpublished* 2010

 **500 nm**



Patterned phase defects

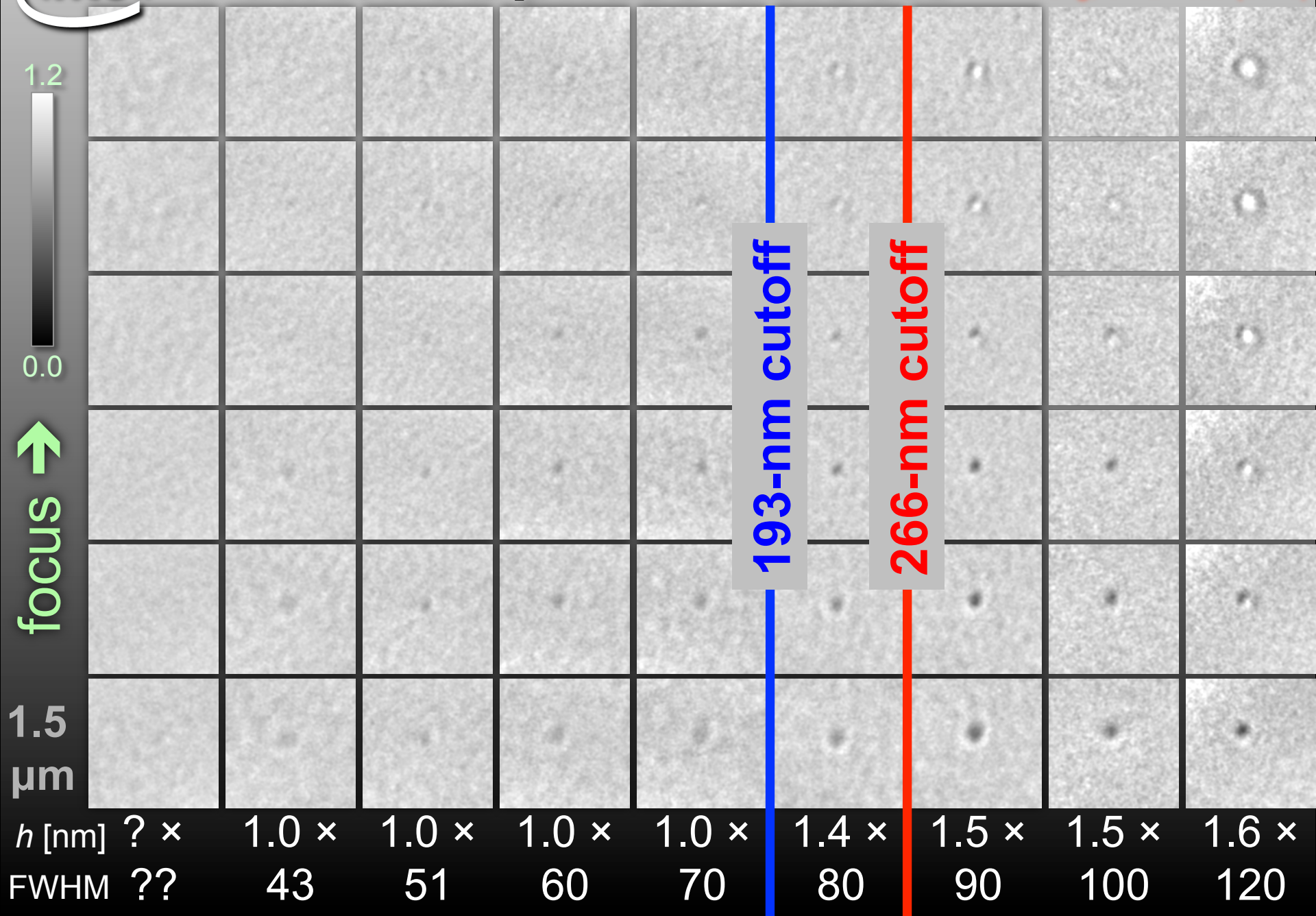
Goldberg, *JVSTB* (2011)
Liang, *SPIE* 7823 (2010)





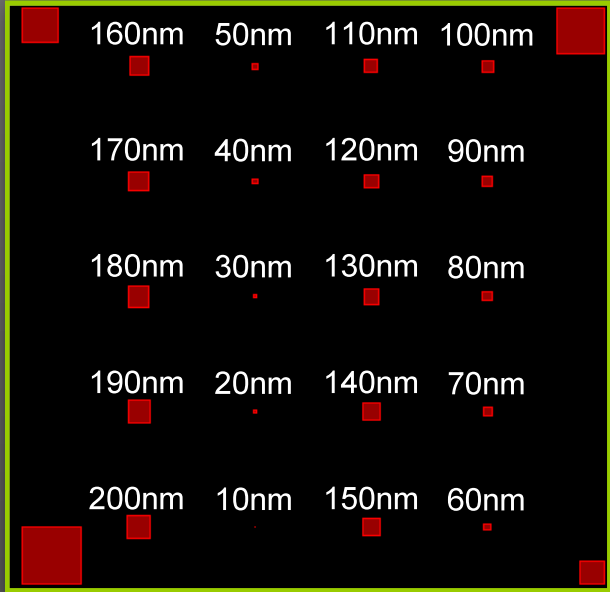
Patterned phase defects

Goldberg, *JVSTB* (2011)
Liang, *SPIE* 7823 (2010)

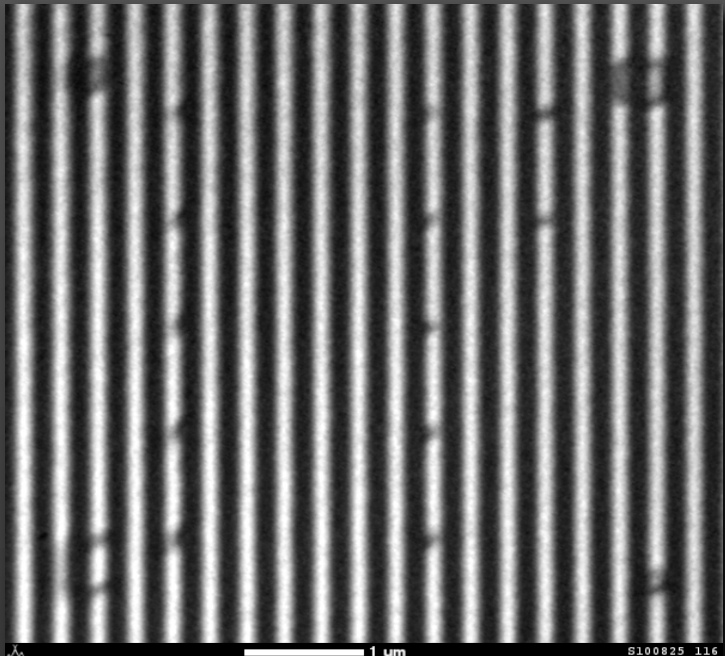




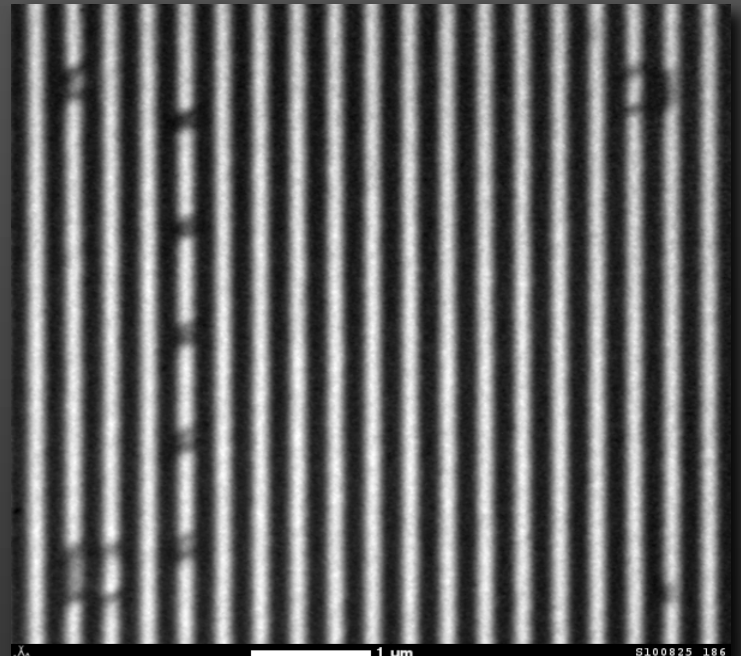
Buried phase defects



AIT Images

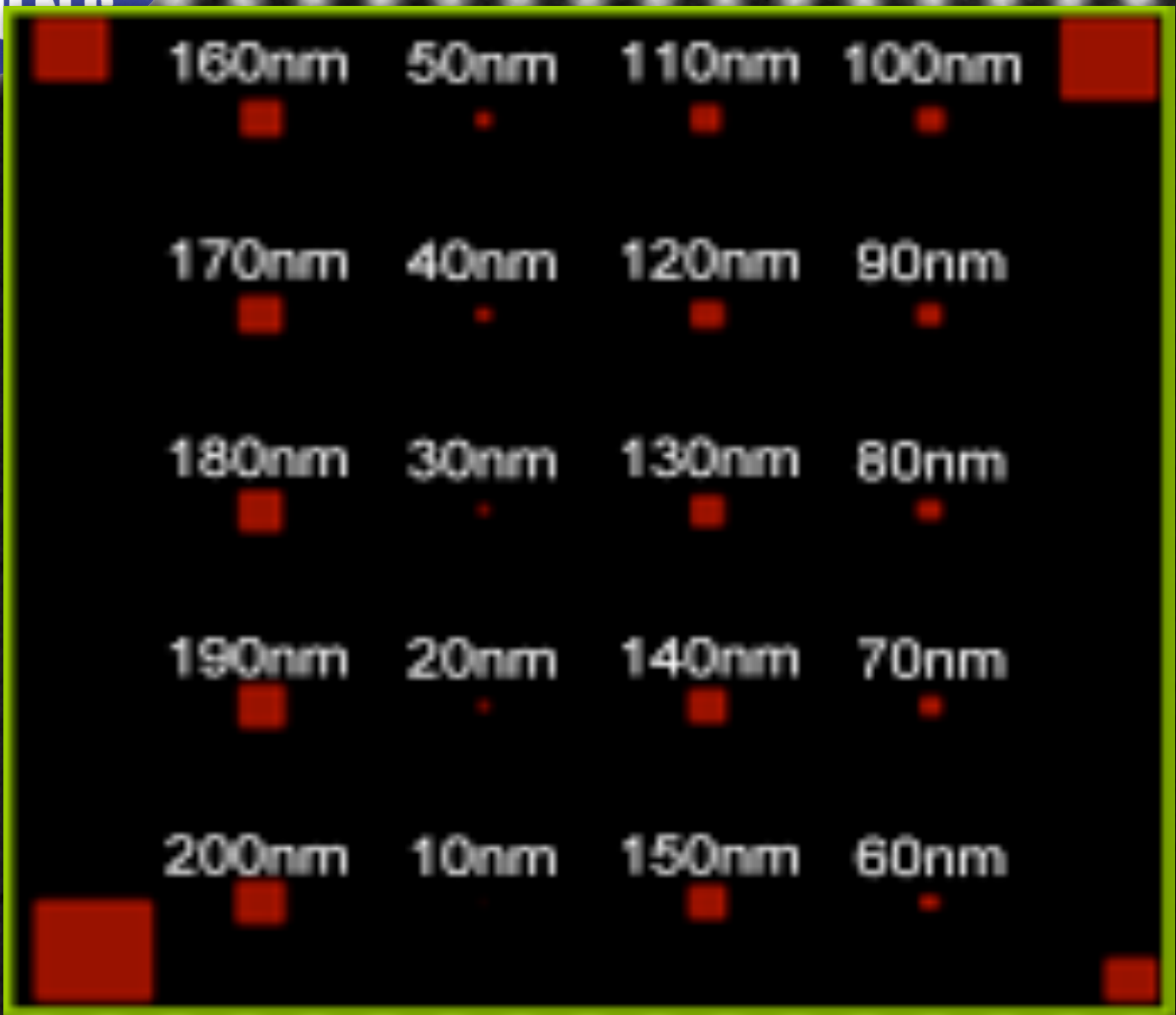


A pattern position shift. . .



covers the defects

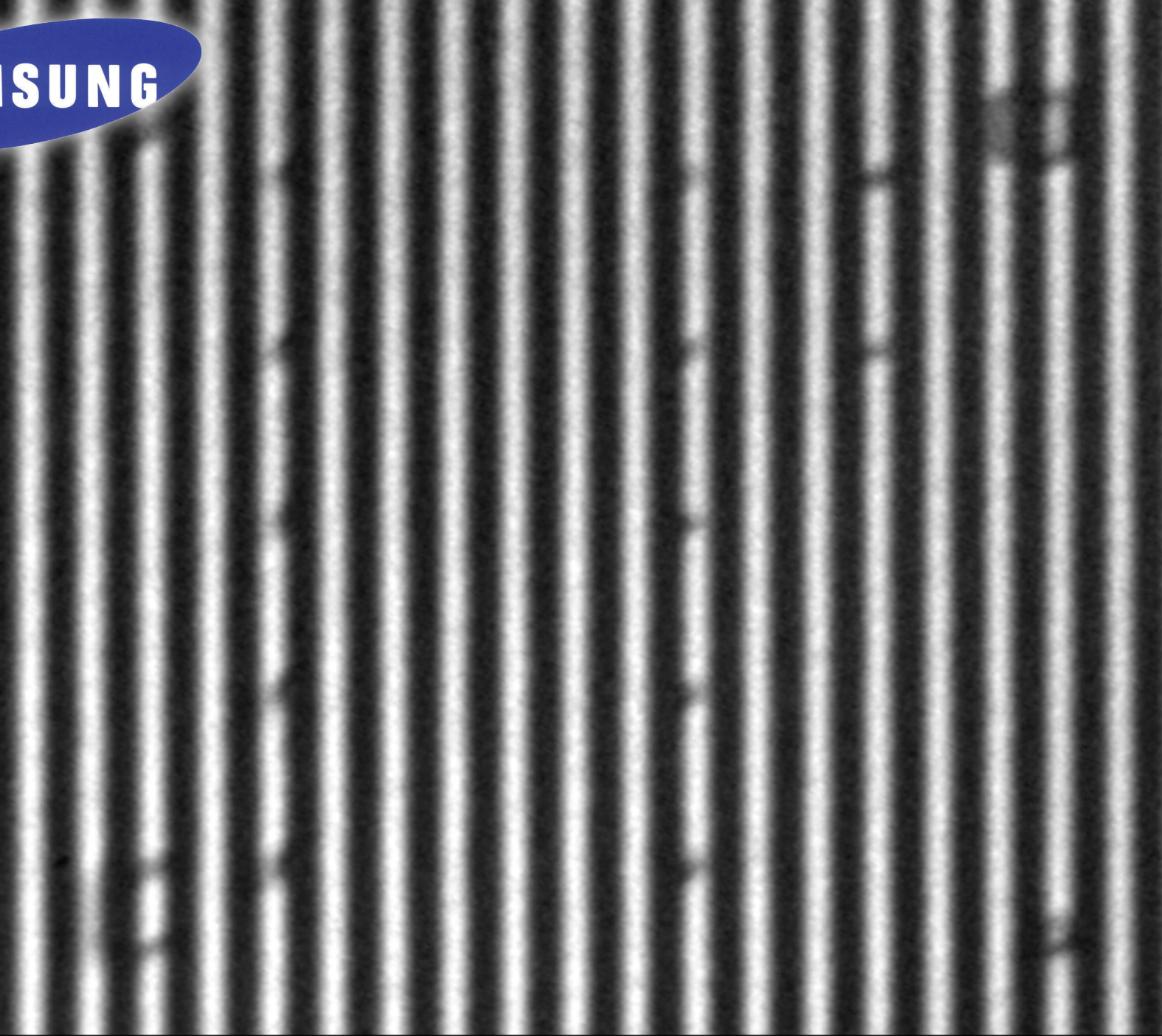
SAMSUNG



1 μm

S100825_116

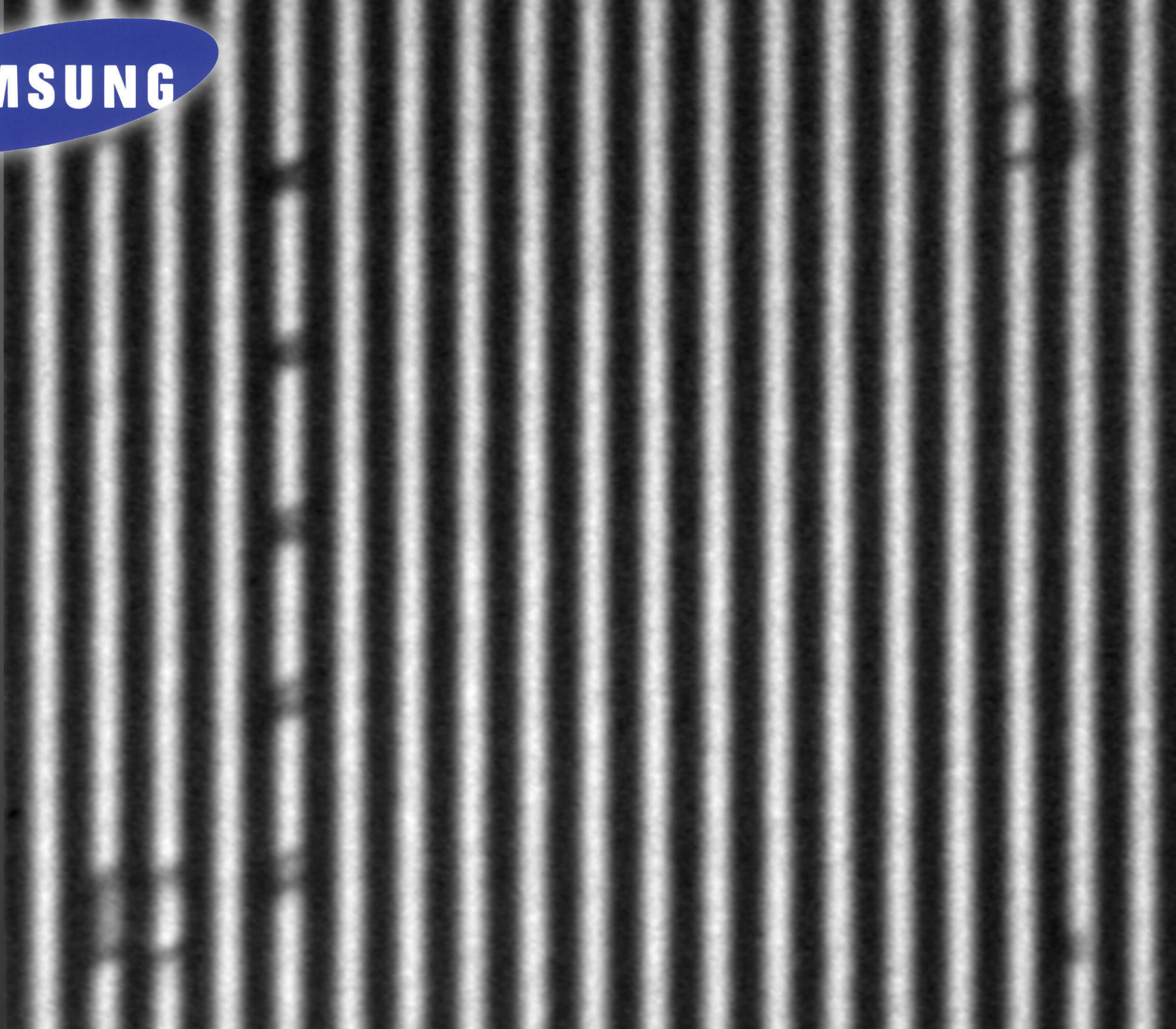
SAMSUNG



1 um

S100825_116

SAMSUNG

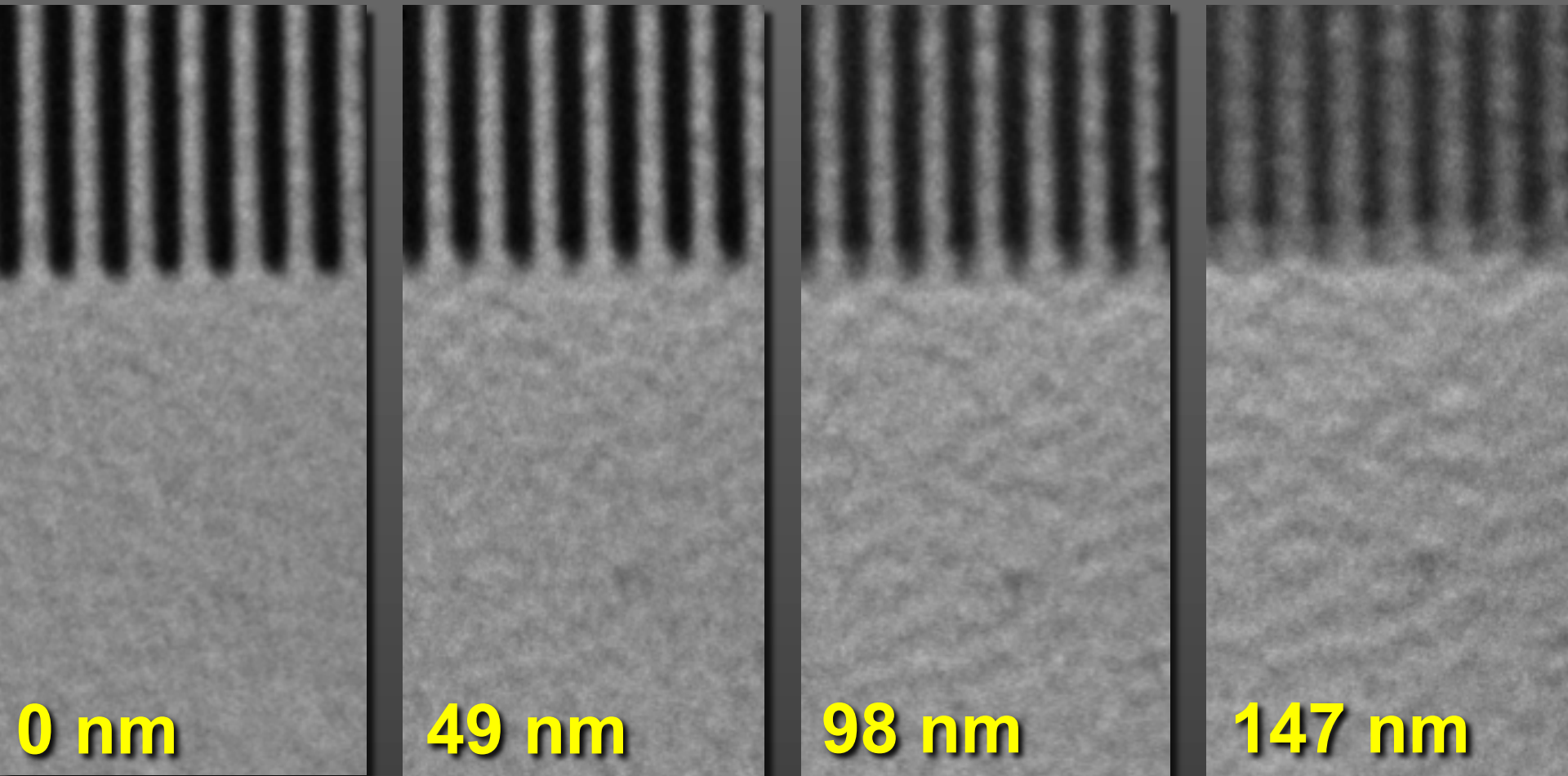


1 um

S100825_186

S. Huh, SPIE 2011

Speckle from ML phase roughness



0 nm

49 nm

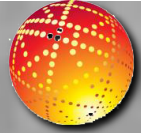
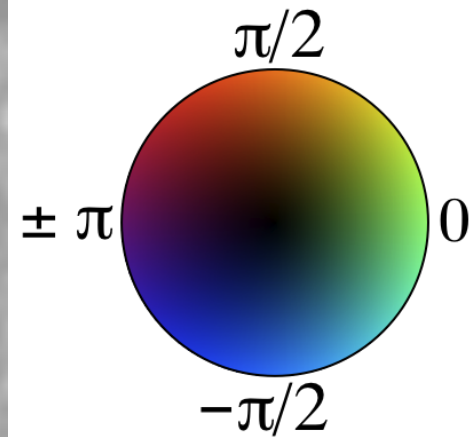
98 nm

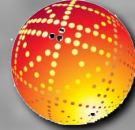
147 nm

Focus →

CXR

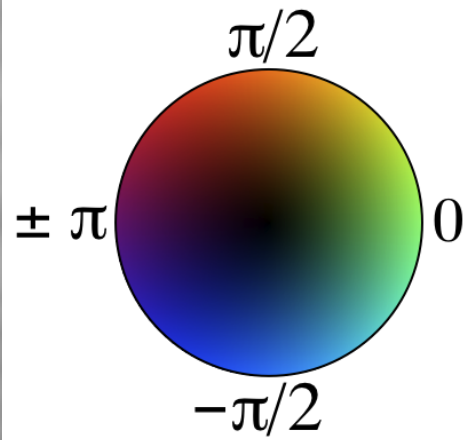
SEMATECH

**See Poster:*****I. Mochi***
7969-67**0.5 μm** ***Phase imaging***



See *Poster:*

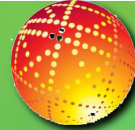
I. Mochi
7969-67



0.5 μm

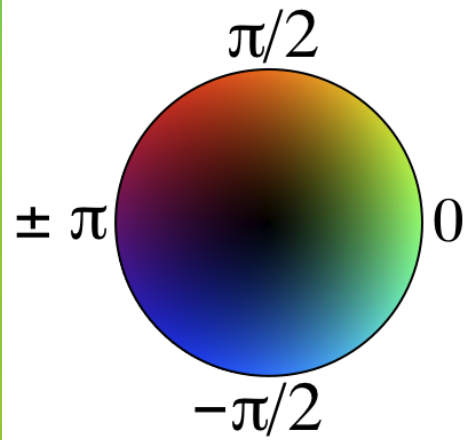
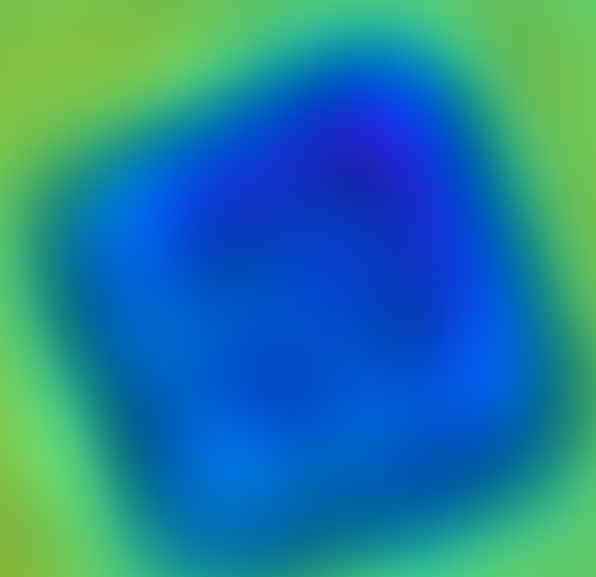


Phase imaging



See *Poster:*

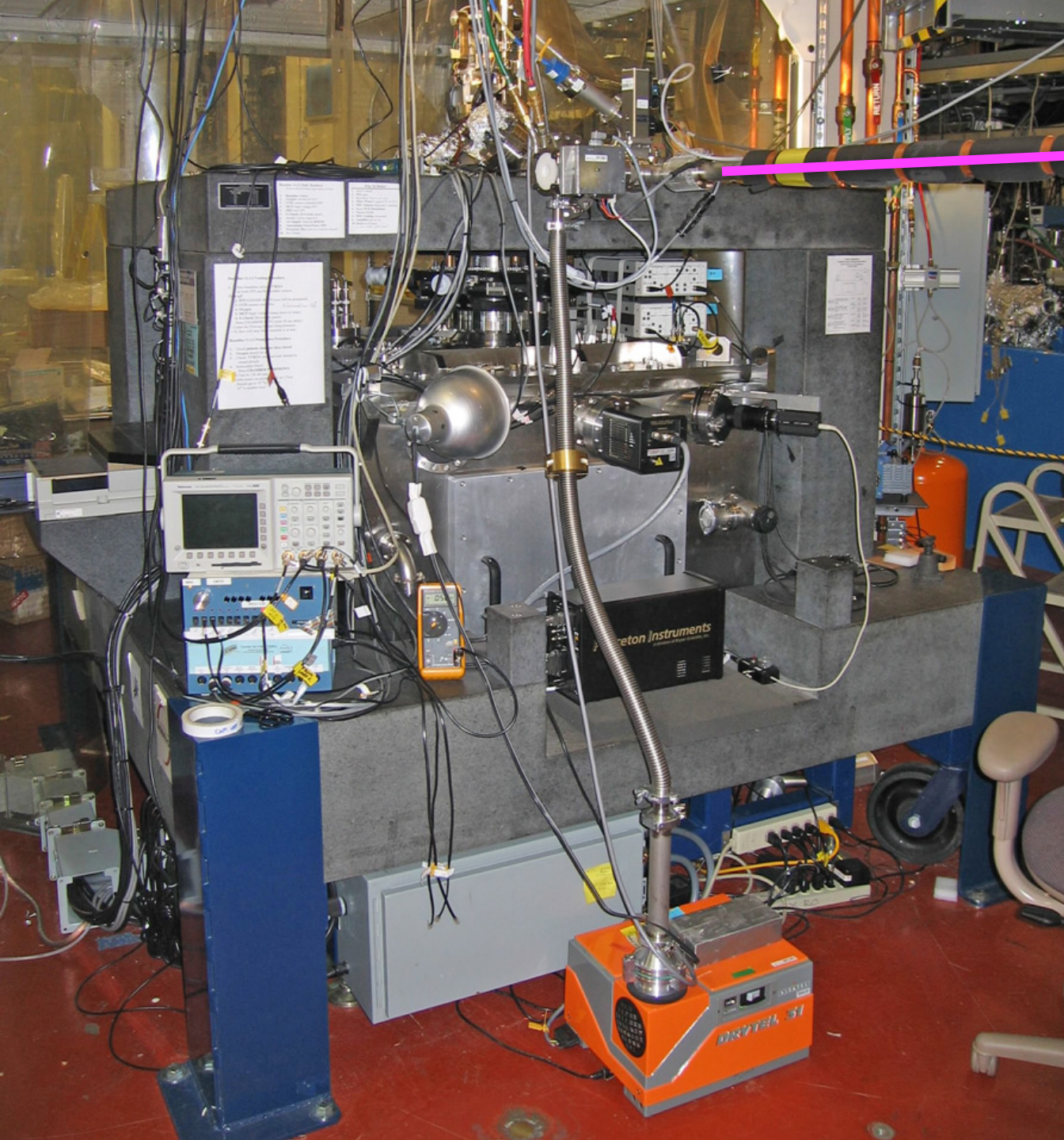
I. Mochi
7969-67



0.5 μm

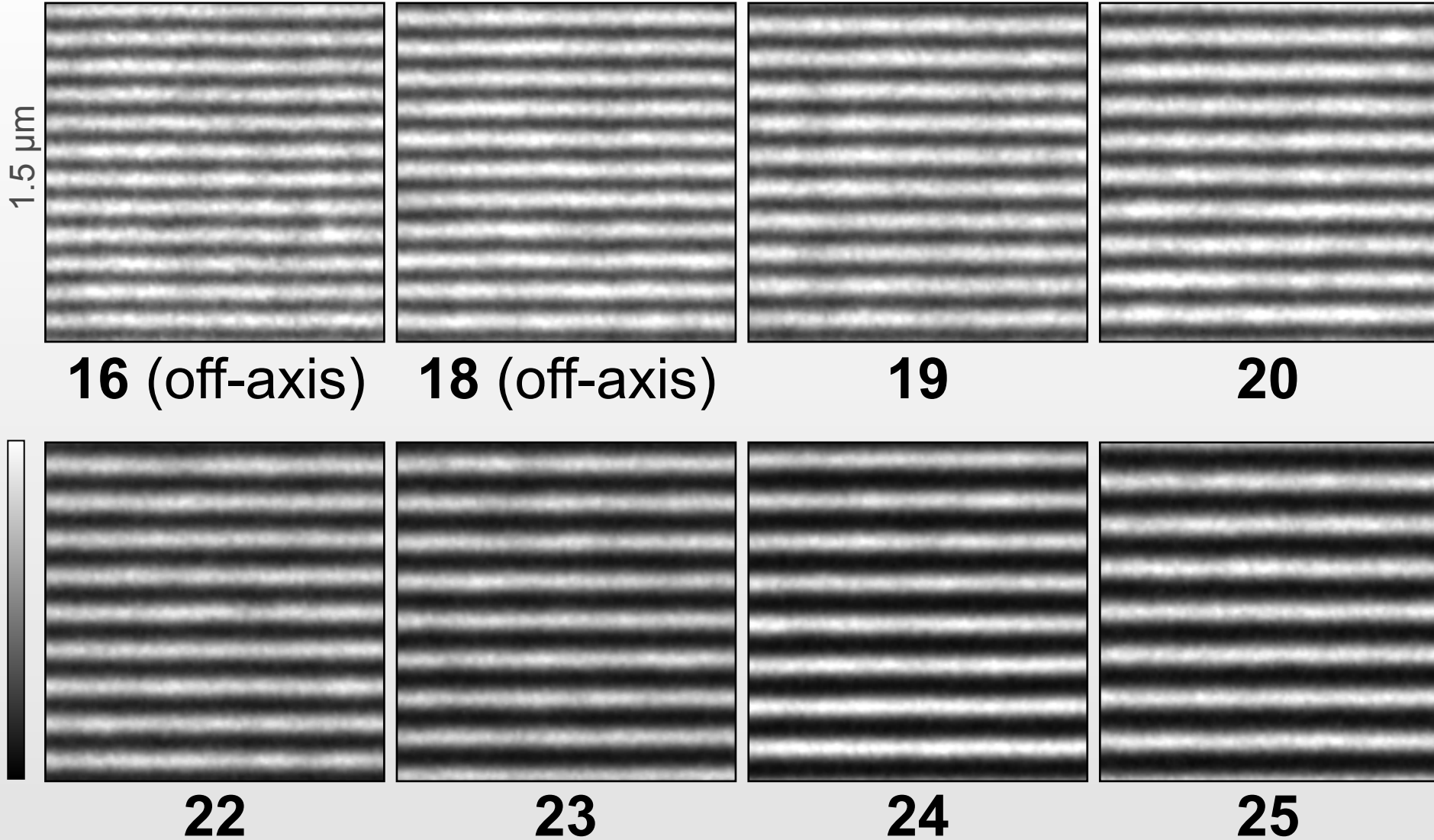


Phase imaging

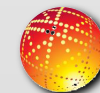


The AIT

The ALT's line contrast reaches down to 16 nm



wafer CD @ 0.35 4xNA



GLOBALFOUNDRIES

Wallow, Mochi, Goldberg: Mask MET10

AIT: Calculated performance

8 nm

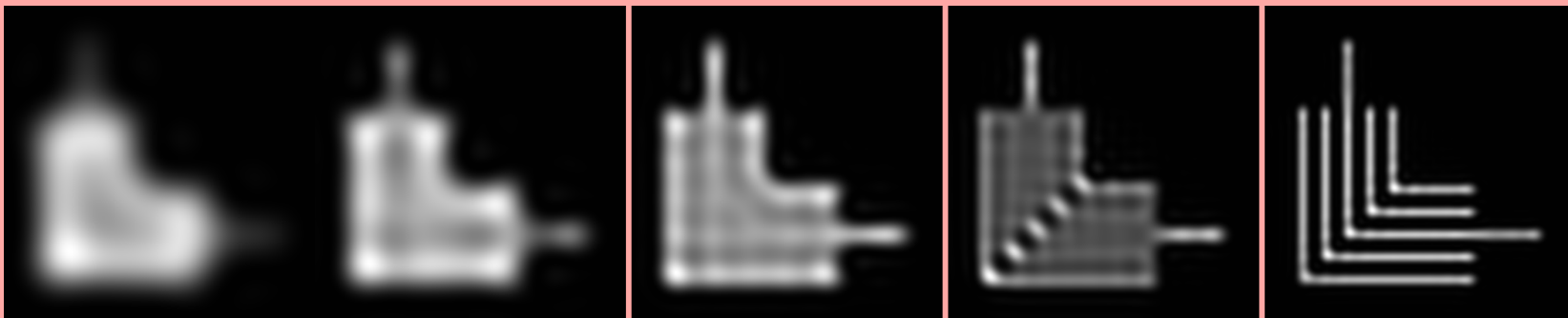
11 nm

16 nm

22 nm

32 nm

0.25 NA
 $\sim 0.2 \sigma$



0.35 NA
 $\sim 0.2 \sigma$



AIT Limit

The AIT is 7 years old.



That's 65 in *litho* years.

Higher resolution needs high NA and σ control

8 nm

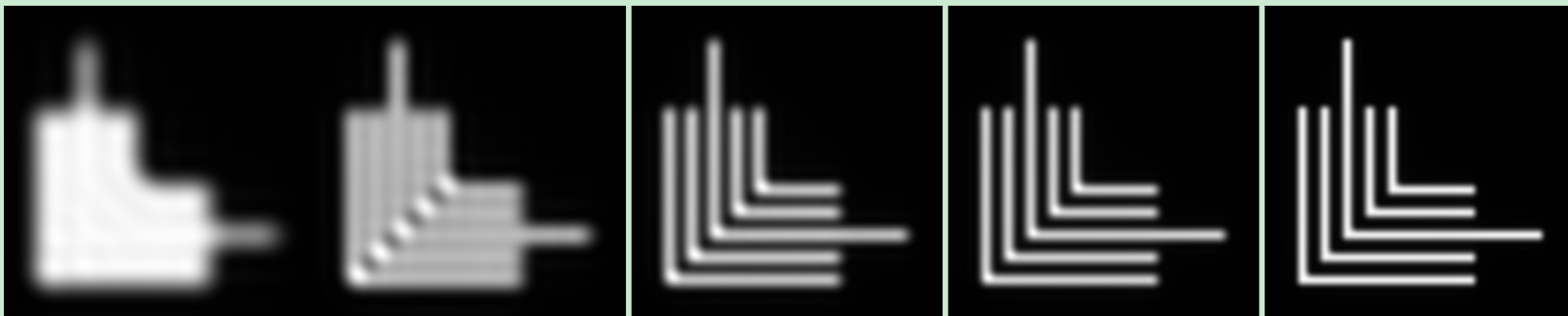
11 nm

16 nm

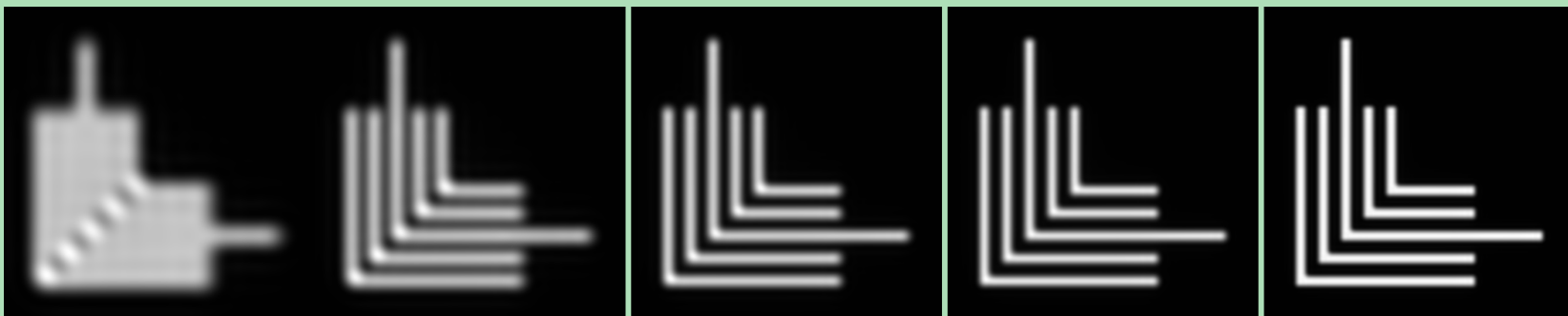
22 nm

32 nm

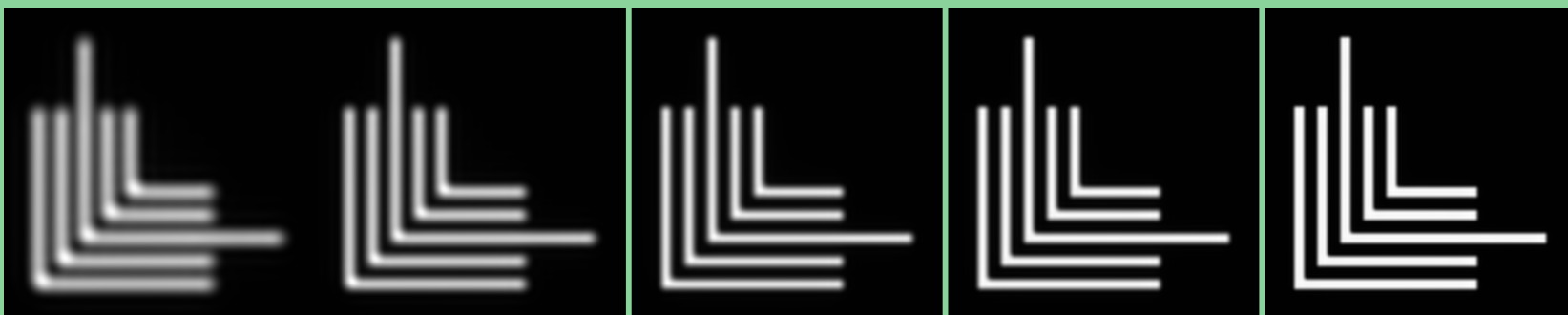
0.35 NA
0.8 σ



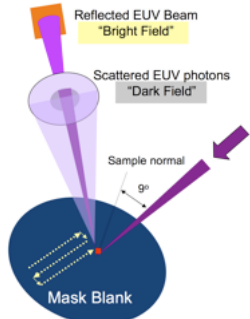
0.45 NA
0.8 σ



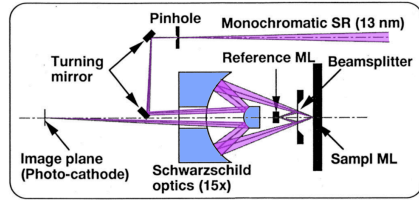
0.62 NA
0.8 σ



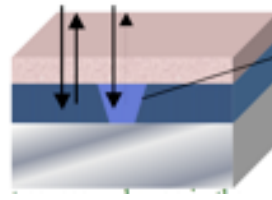
13+ years of actinic mask inspection/imaging



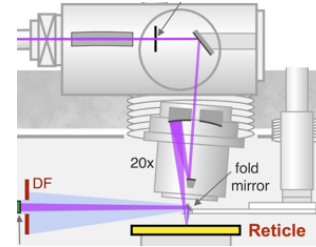
EUV LLC/LBNL



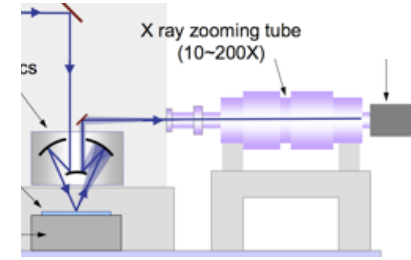
NTT



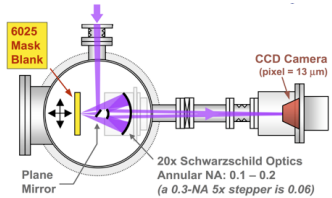
Lucent



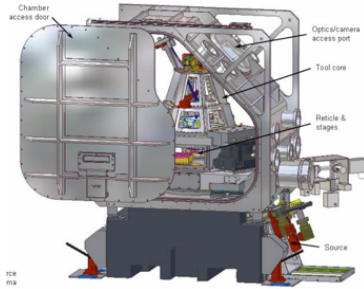
SEMATECH/LBNL



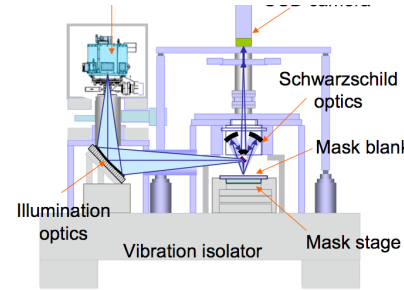
U. Hyogo



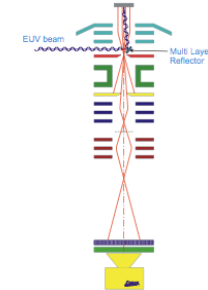
MIRAI



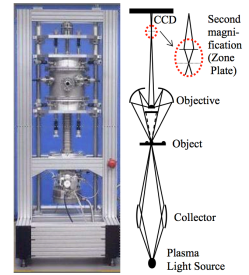
Exitech



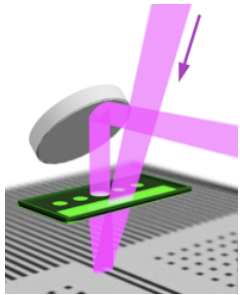
MIRAI II/Selete



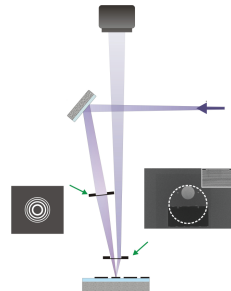
U. Bielefeld



Fraunhofer Institute



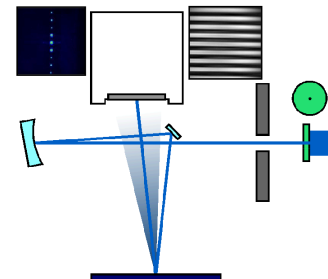
SEMATECH/LBNL



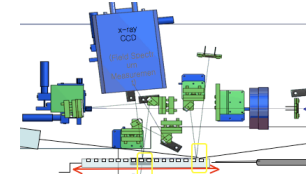
Colorado State



INVENT/CNSE



U. Hyogo



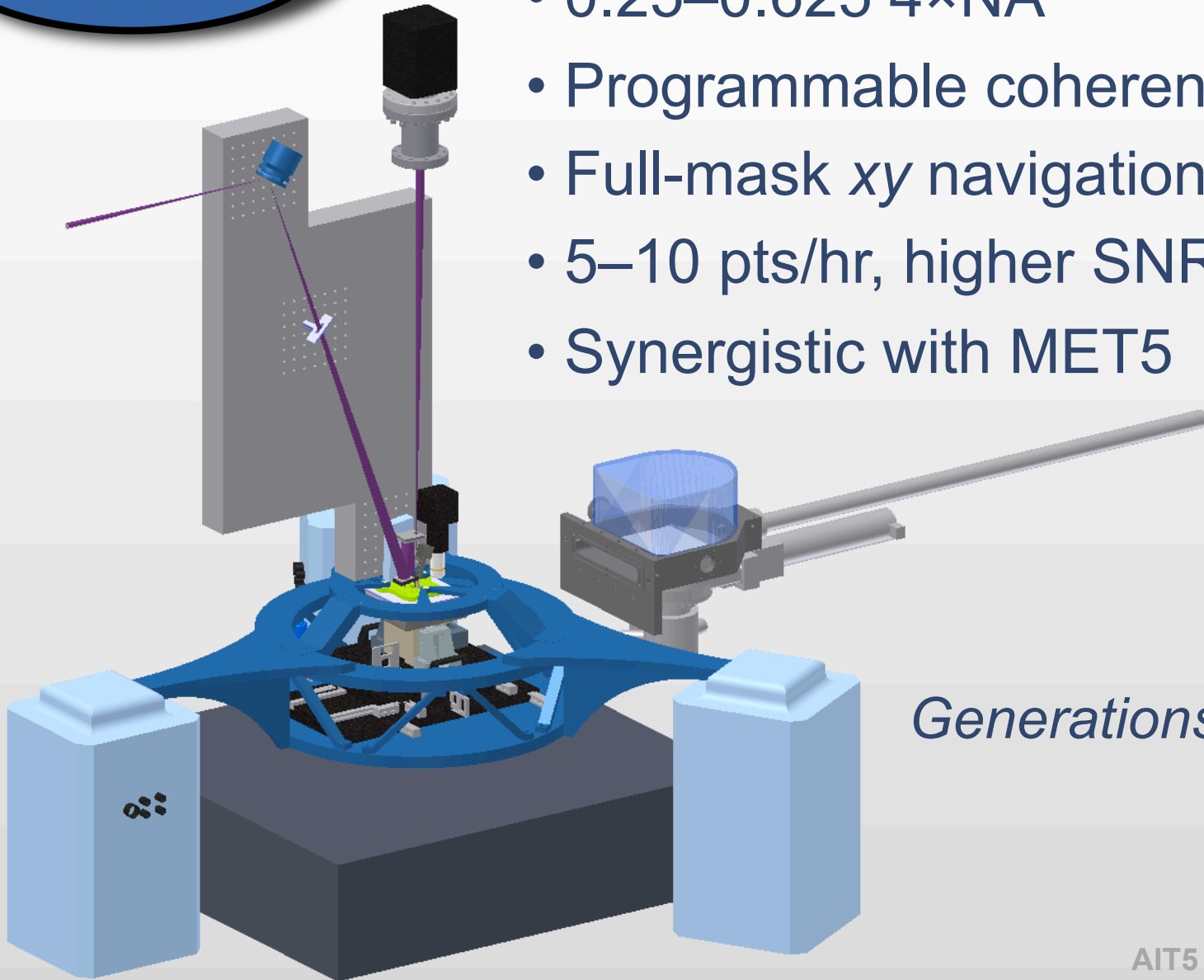
Hanyang



Zeiss future

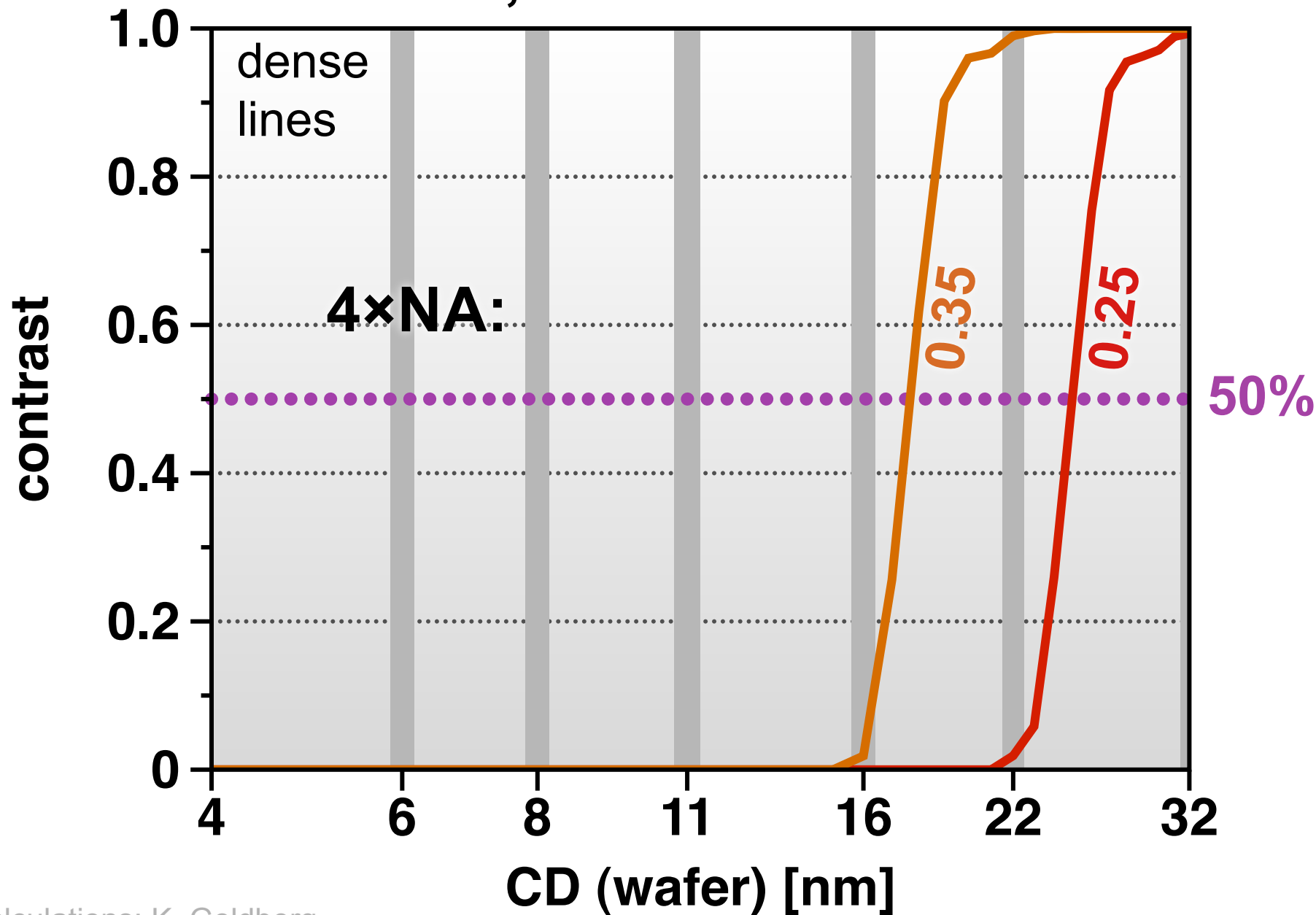
AIT5

- Zoneplate-lens imaging
- 0.25–0.625 4×NA
- Programmable coherence, σ
- Full-mask xy navigation
- 5–10 pts/hr, higher SNR
- Synergistic with MET5

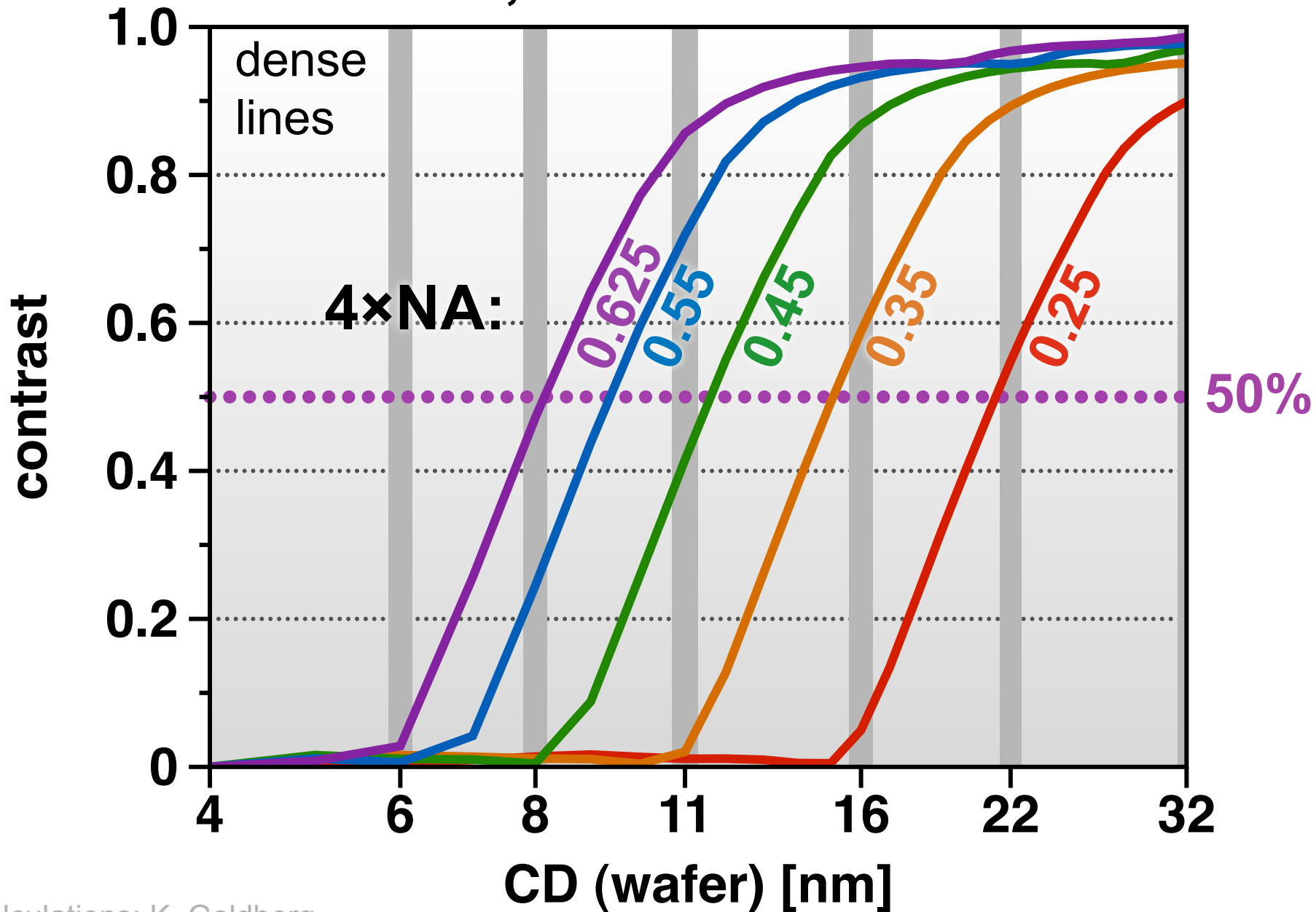


Generations Ahead

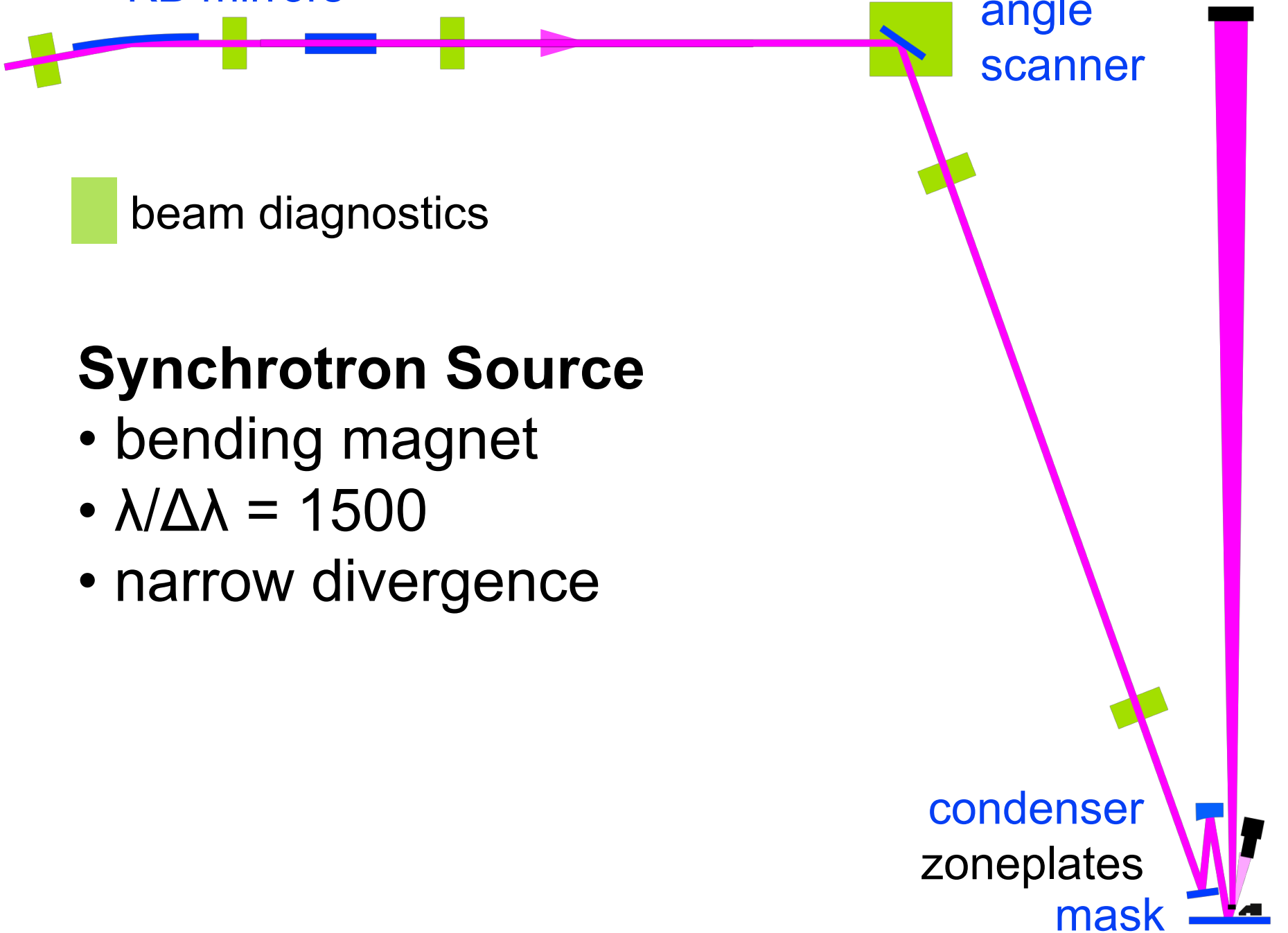
At $\sigma \approx 0.2$, AIT sees ≥ 16 nm



At $\sigma = 0.8$, AIT5 will see > 6 nm



KB mirrors



angle scanner

CCD

■ beam diagnostics

Synchrotron Source

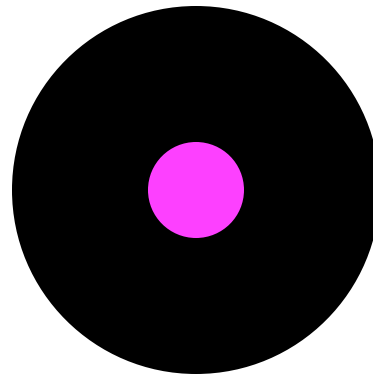
- bending magnet
- $\lambda/\Delta\lambda = 1500$
- narrow divergence

condenser
zoneplates
mask

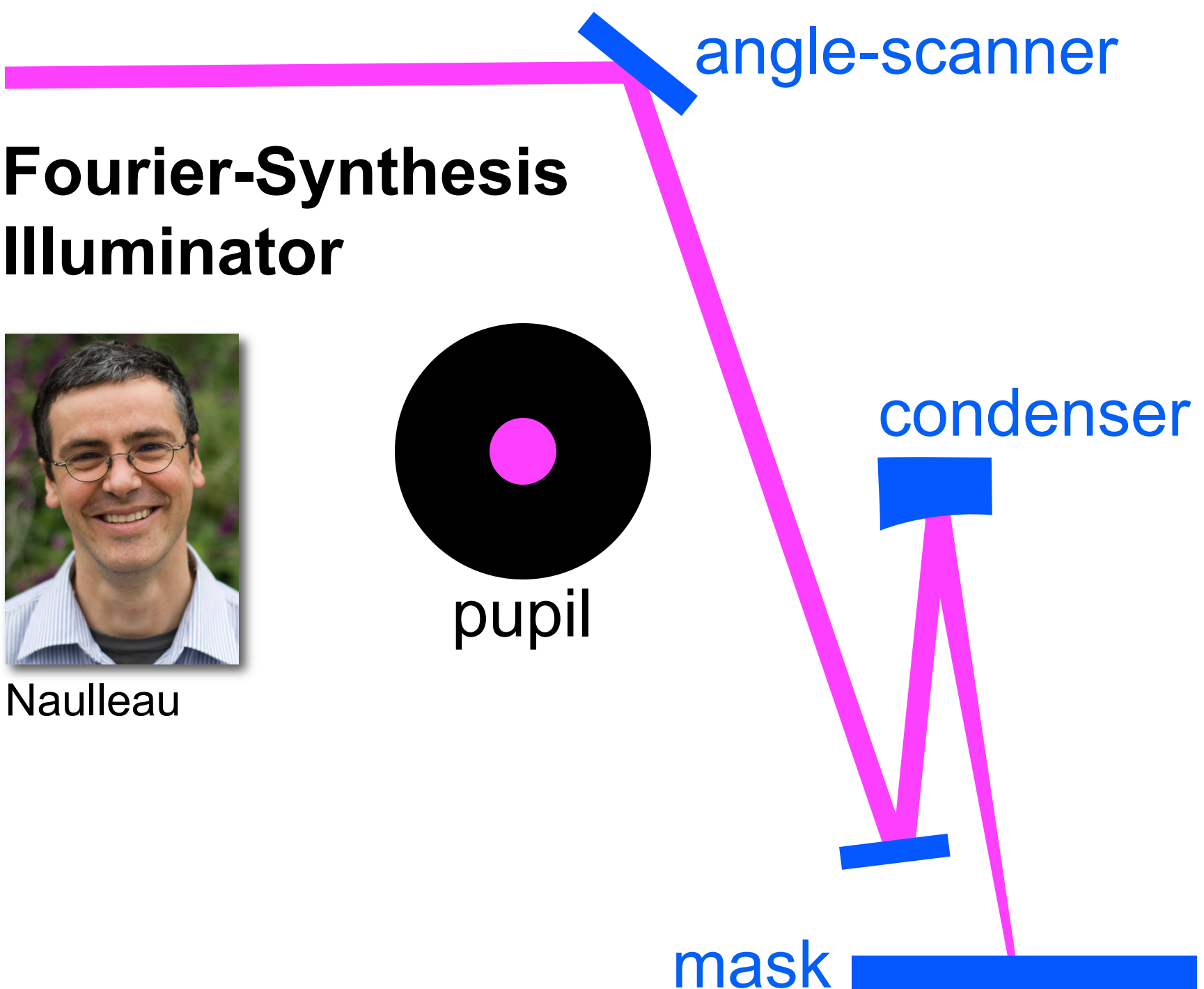
Fourier-Synthesis Illuminator



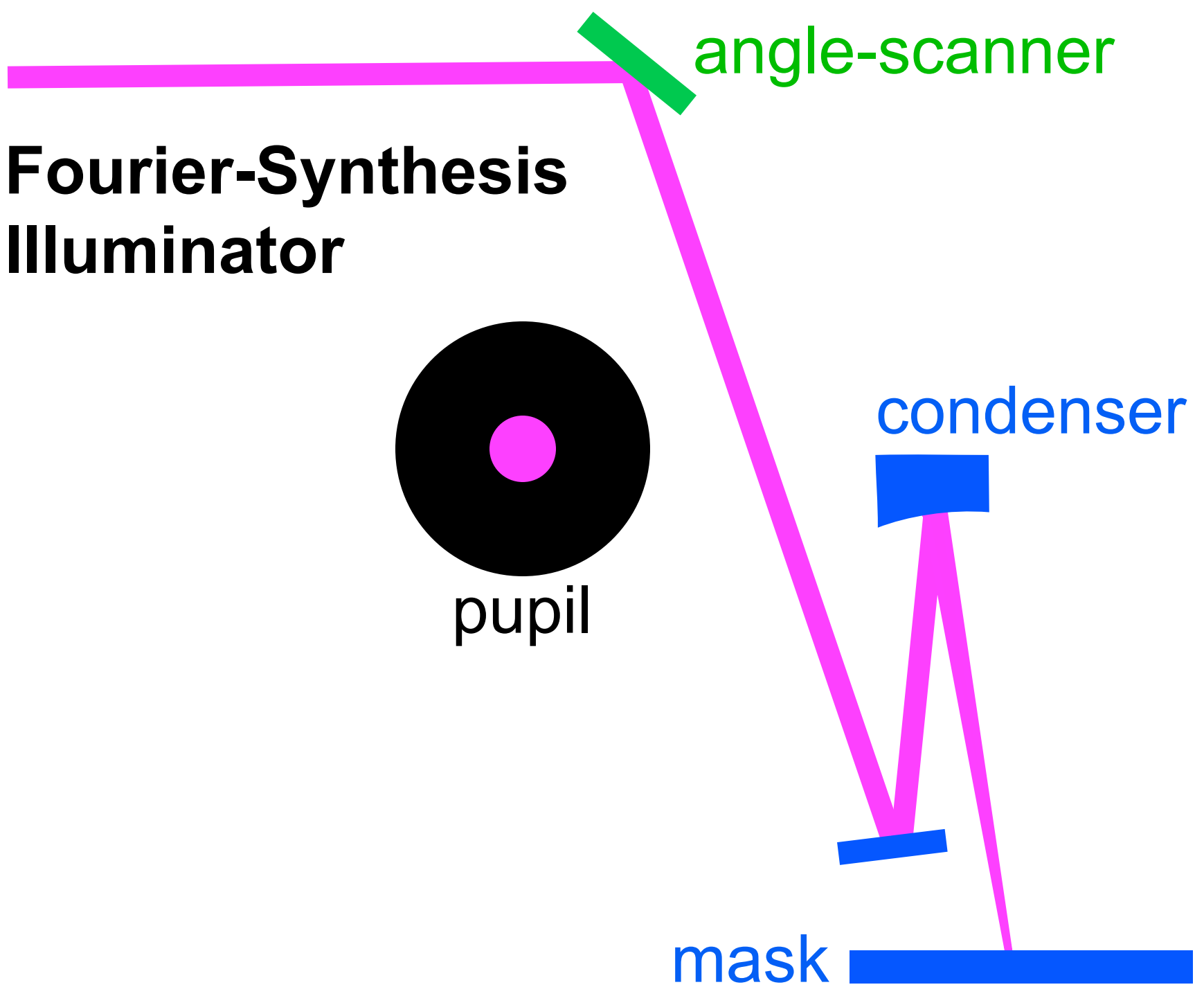
Naulleau



pupil



Fourier-Synthesis Illuminator



angle-scanner

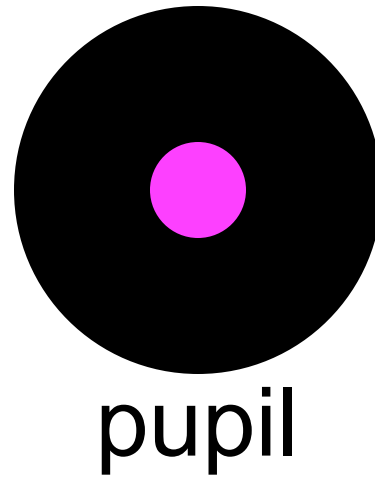
condenser

pupil

mask

mask

Fourier-Synthesis Illuminator



angle-scanner

- diamond-turned
- HSQ smoothed
- ML coated

condenser

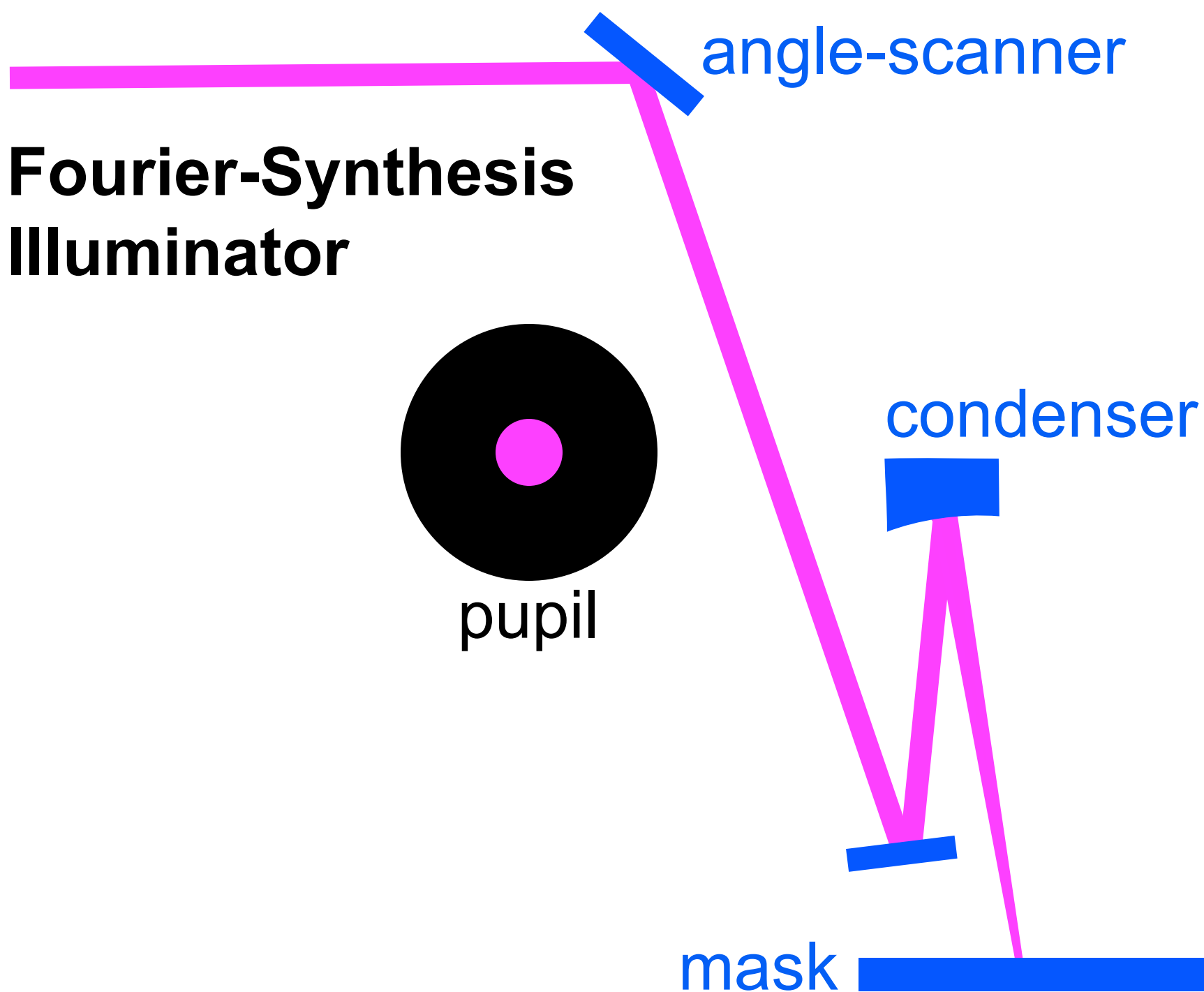


mask

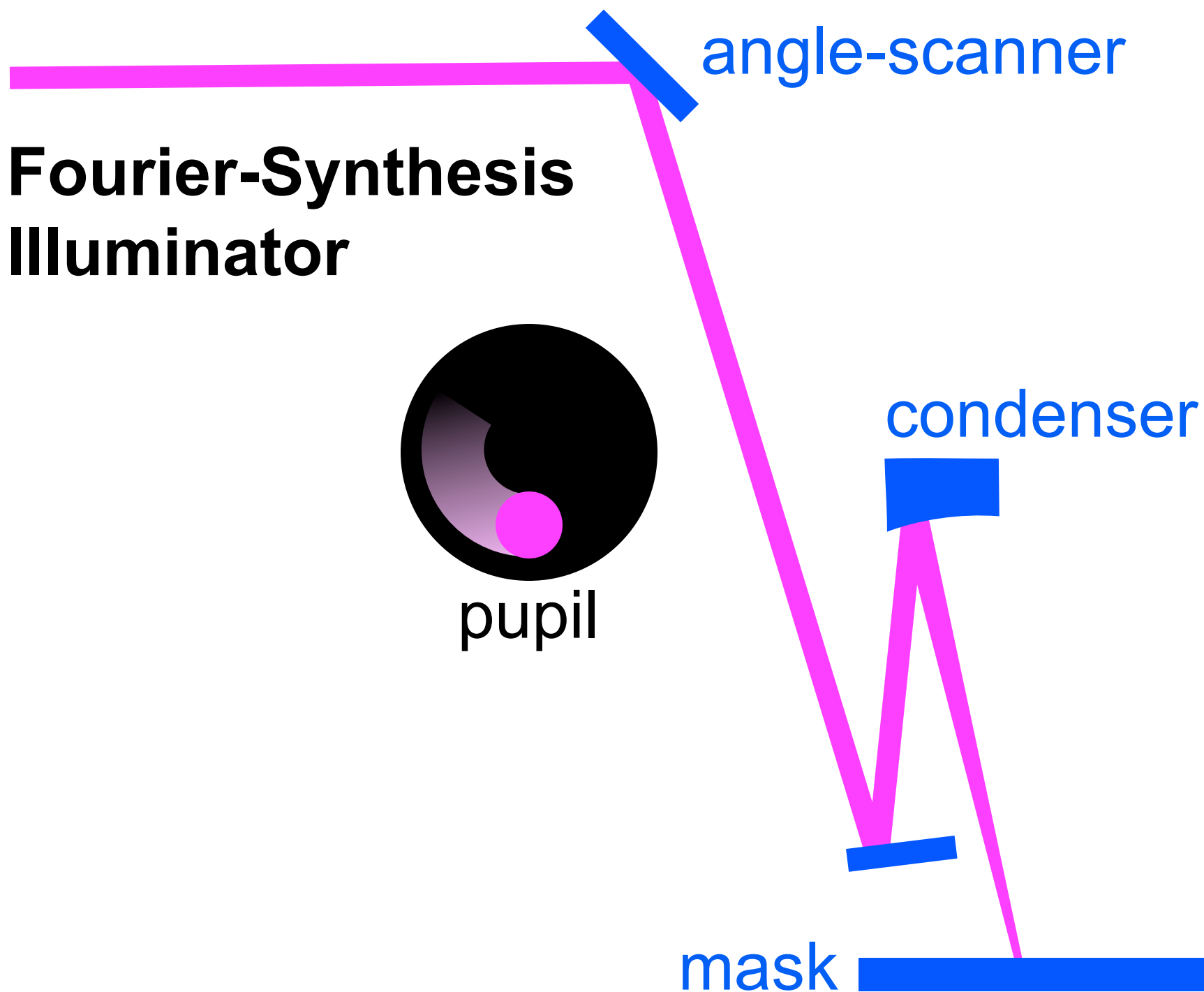
~15 μm

Soufli, *Opt. Eng.* **43** (12), 2004.
Salmassi, *Appl. Opt.* **45** (11), 2006.

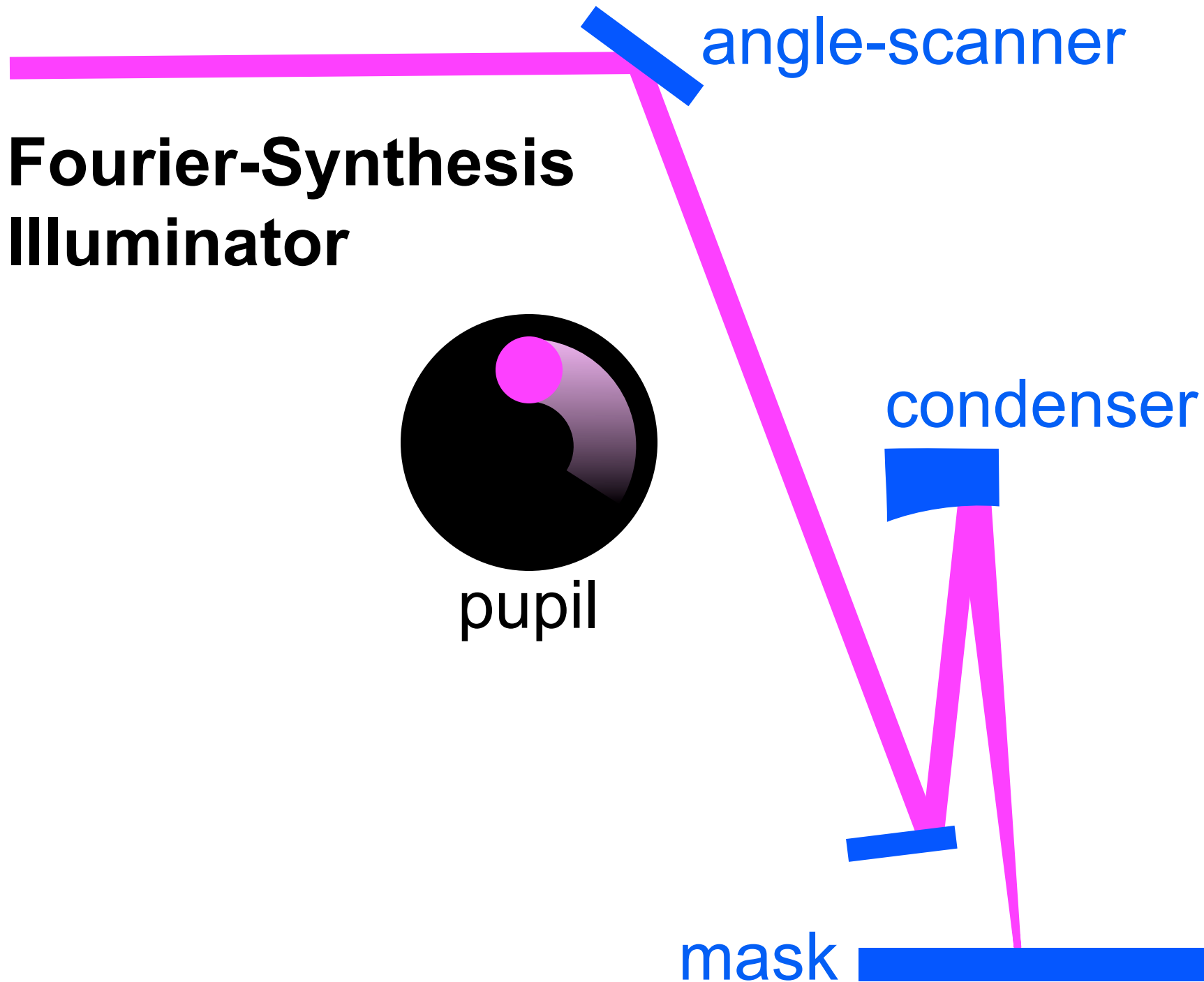
Fourier-Synthesis Illuminator



Fourier-Synthesis Illuminator



Fourier-Synthesis Illuminator



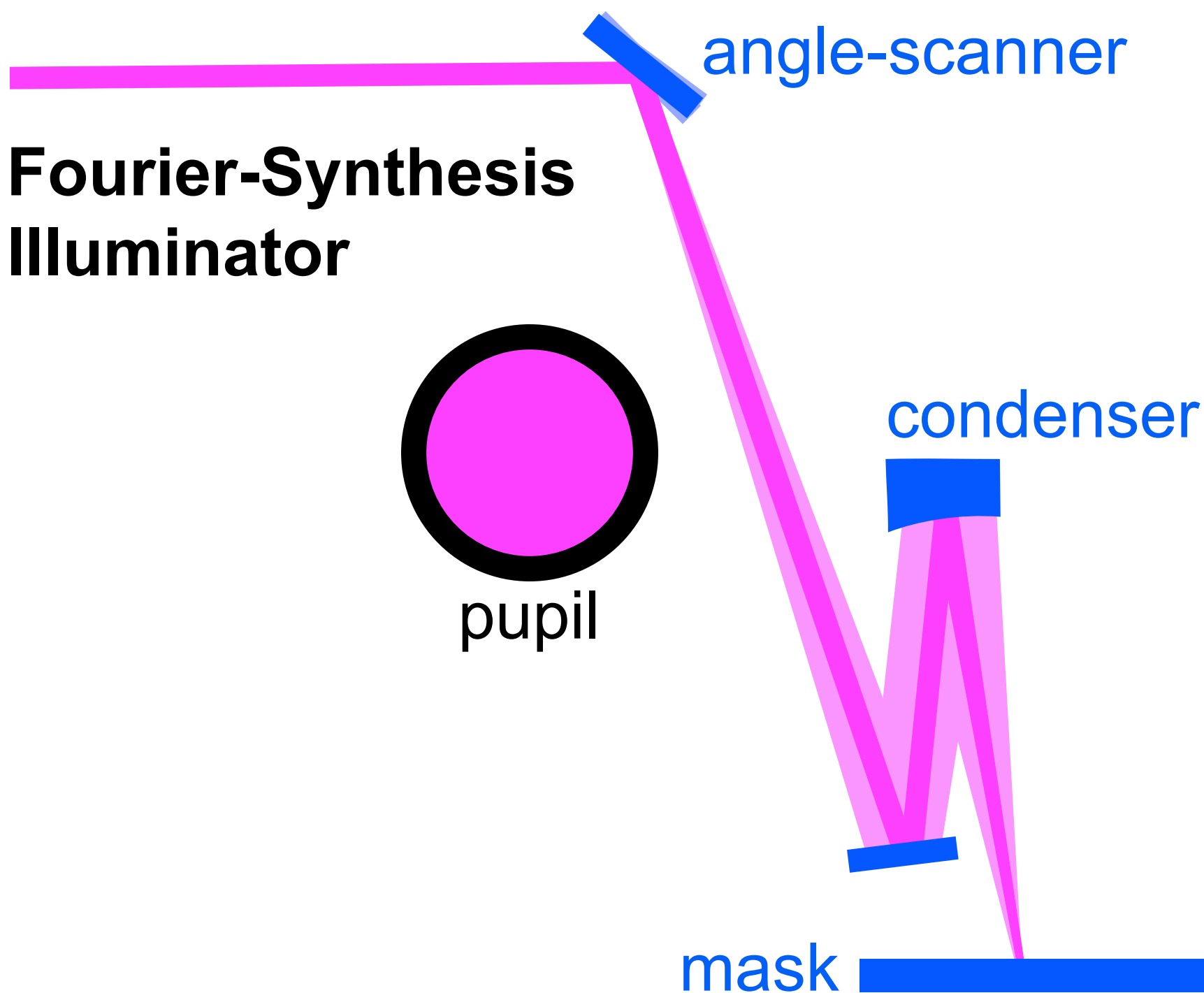
angle-scanner

condenser

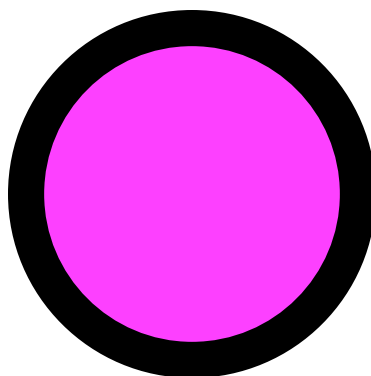
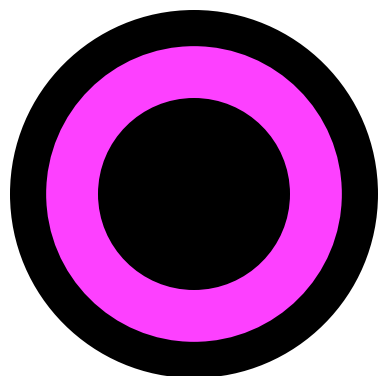
pupil

mask

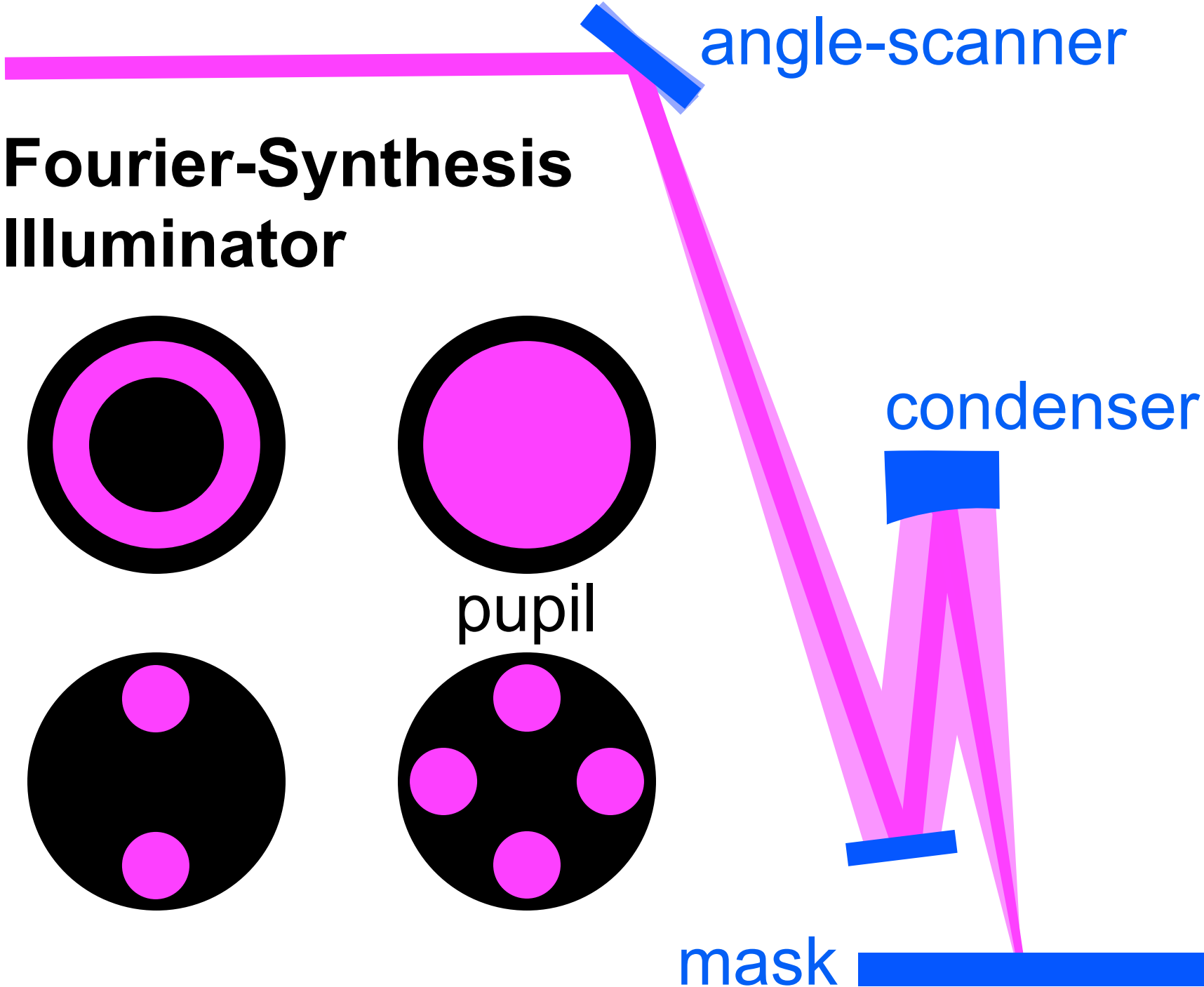
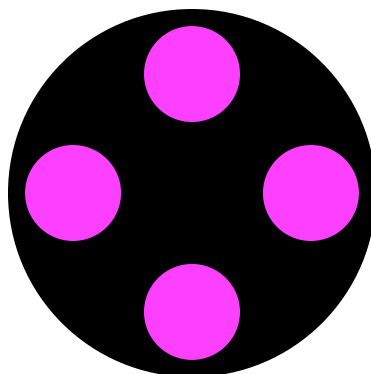
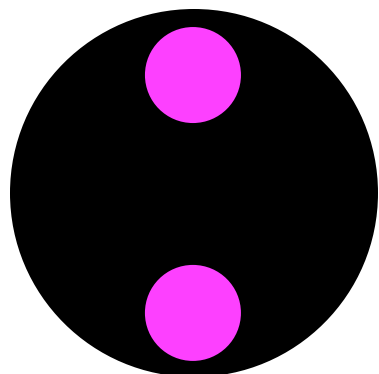
Fourier-Synthesis Illuminator



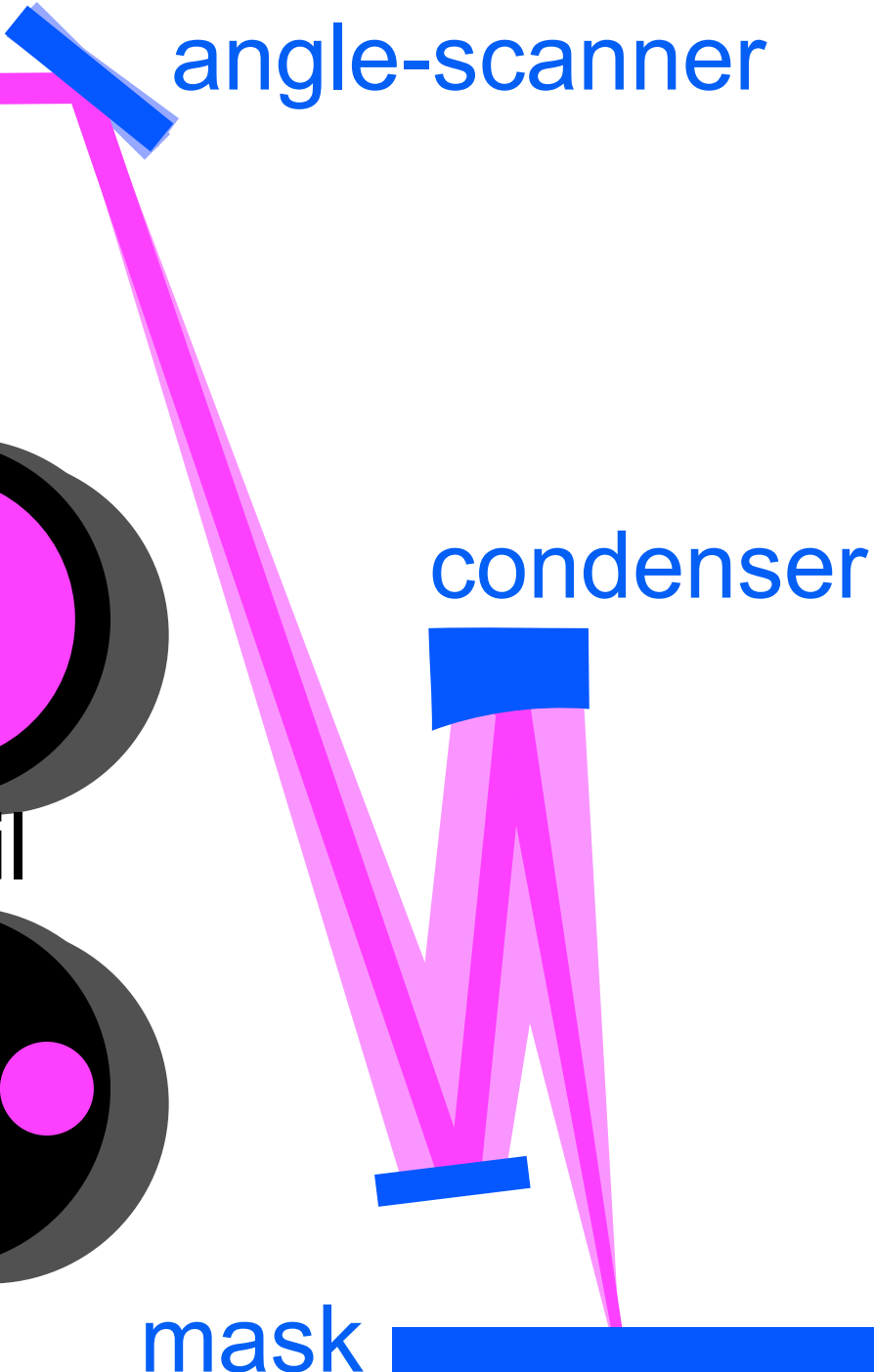
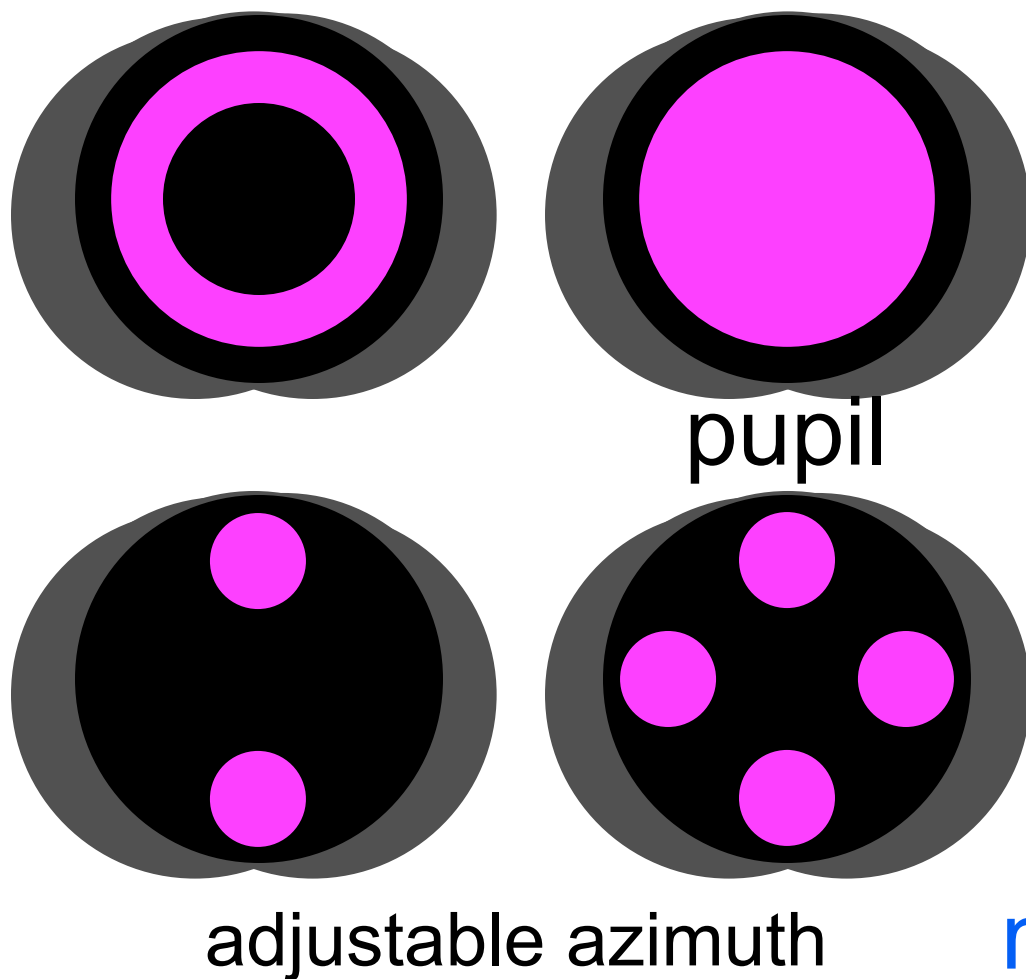
Fourier-Synthesis Illuminator

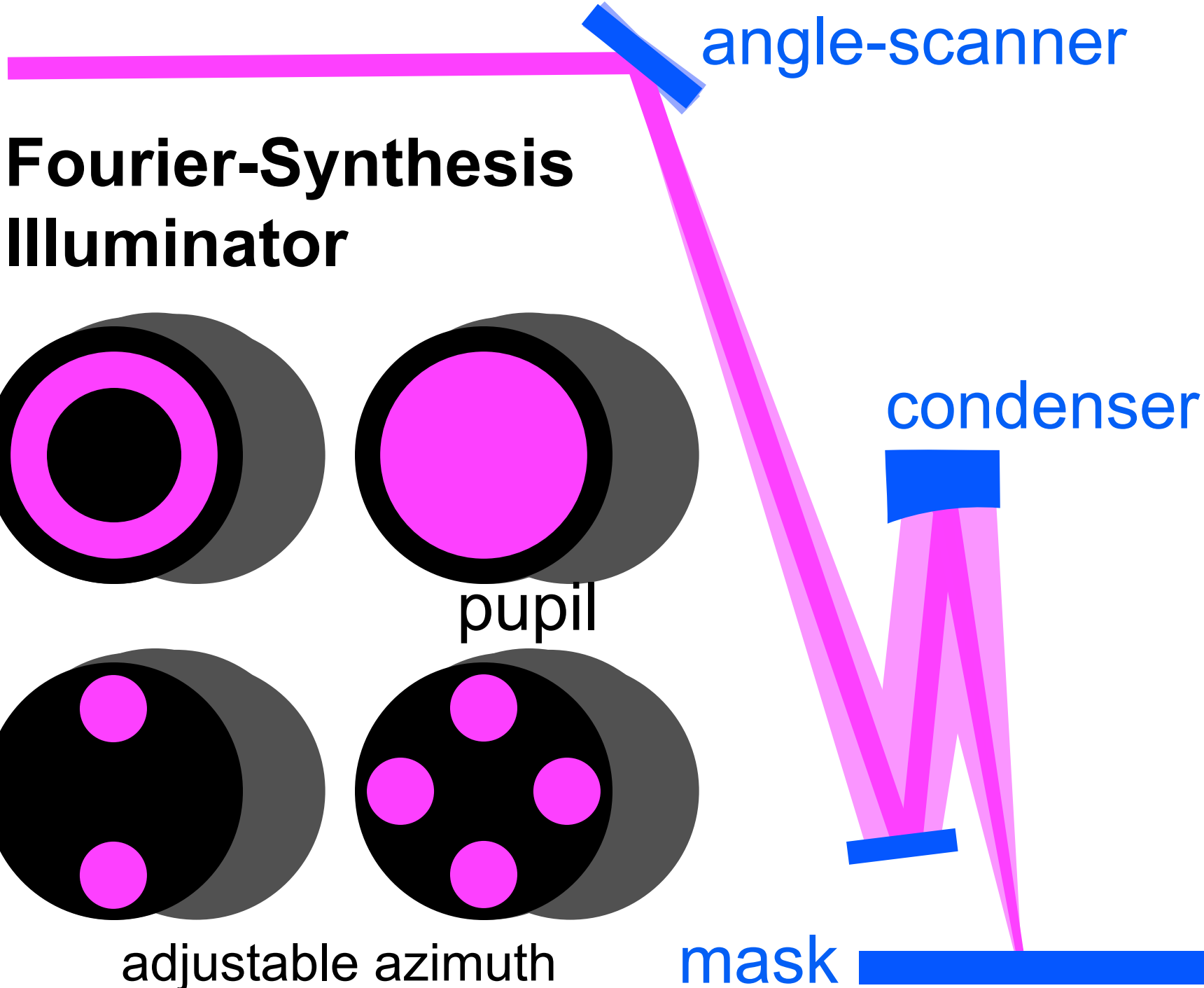


pupil

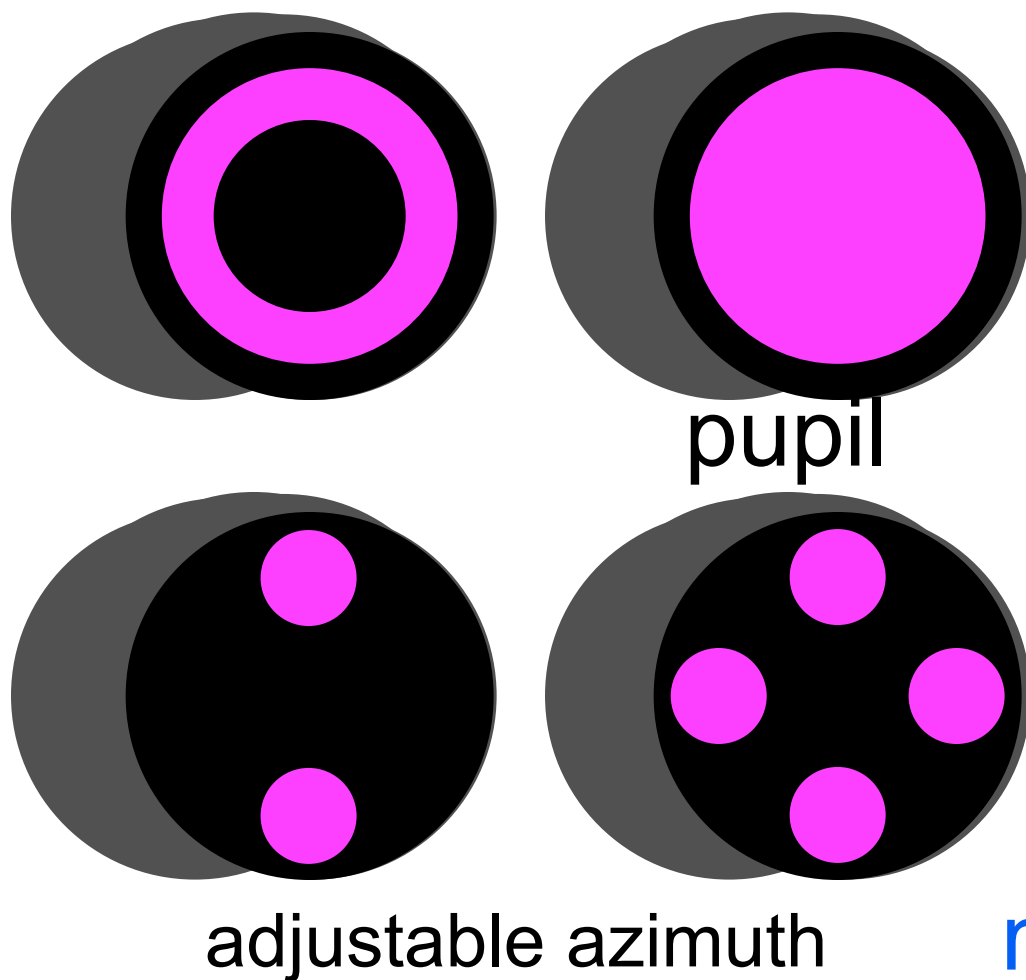


Fourier-Synthesis Illuminator



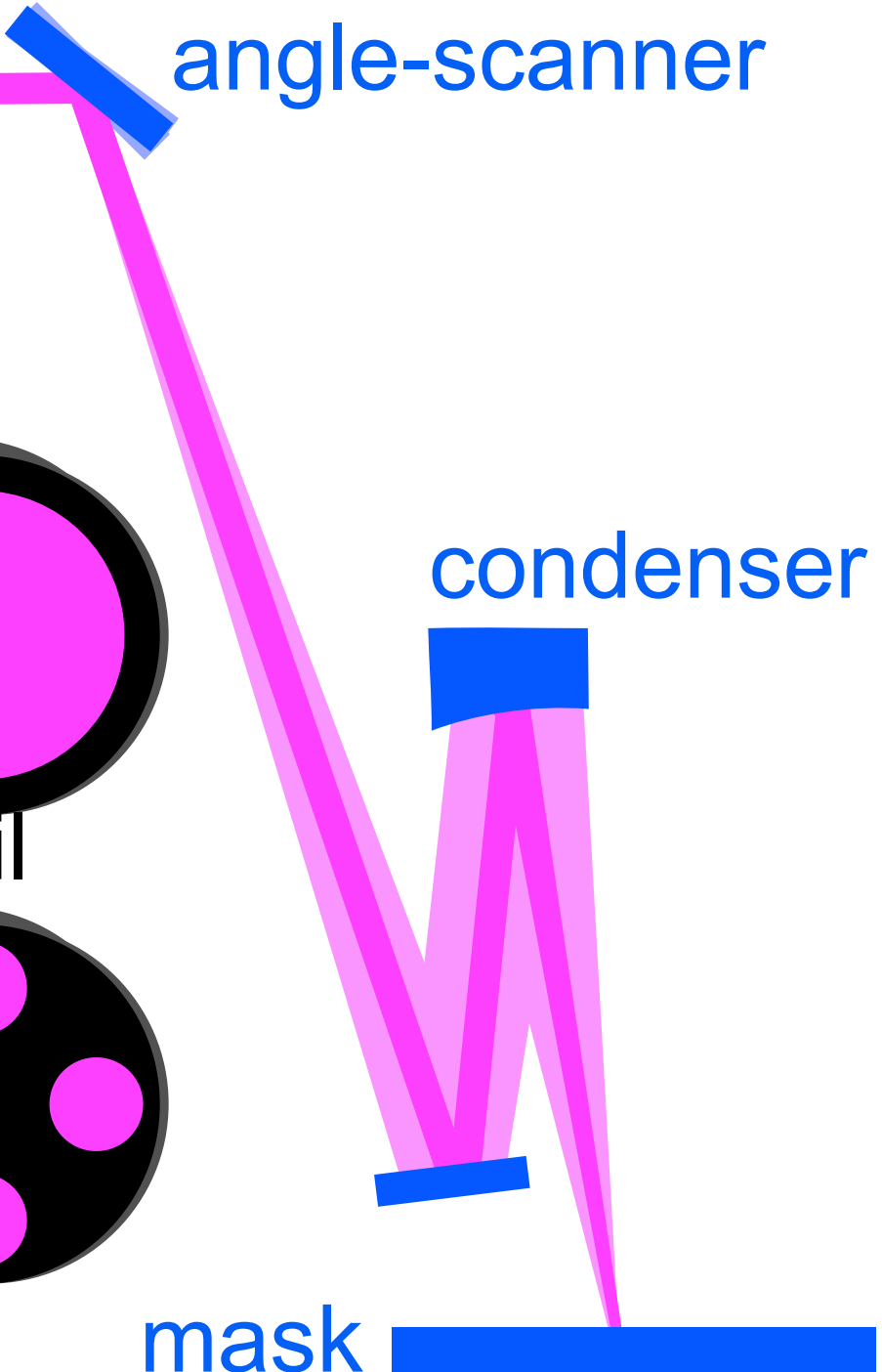


Fourier-Synthesis Illuminator



pupil

adjustable azimuth

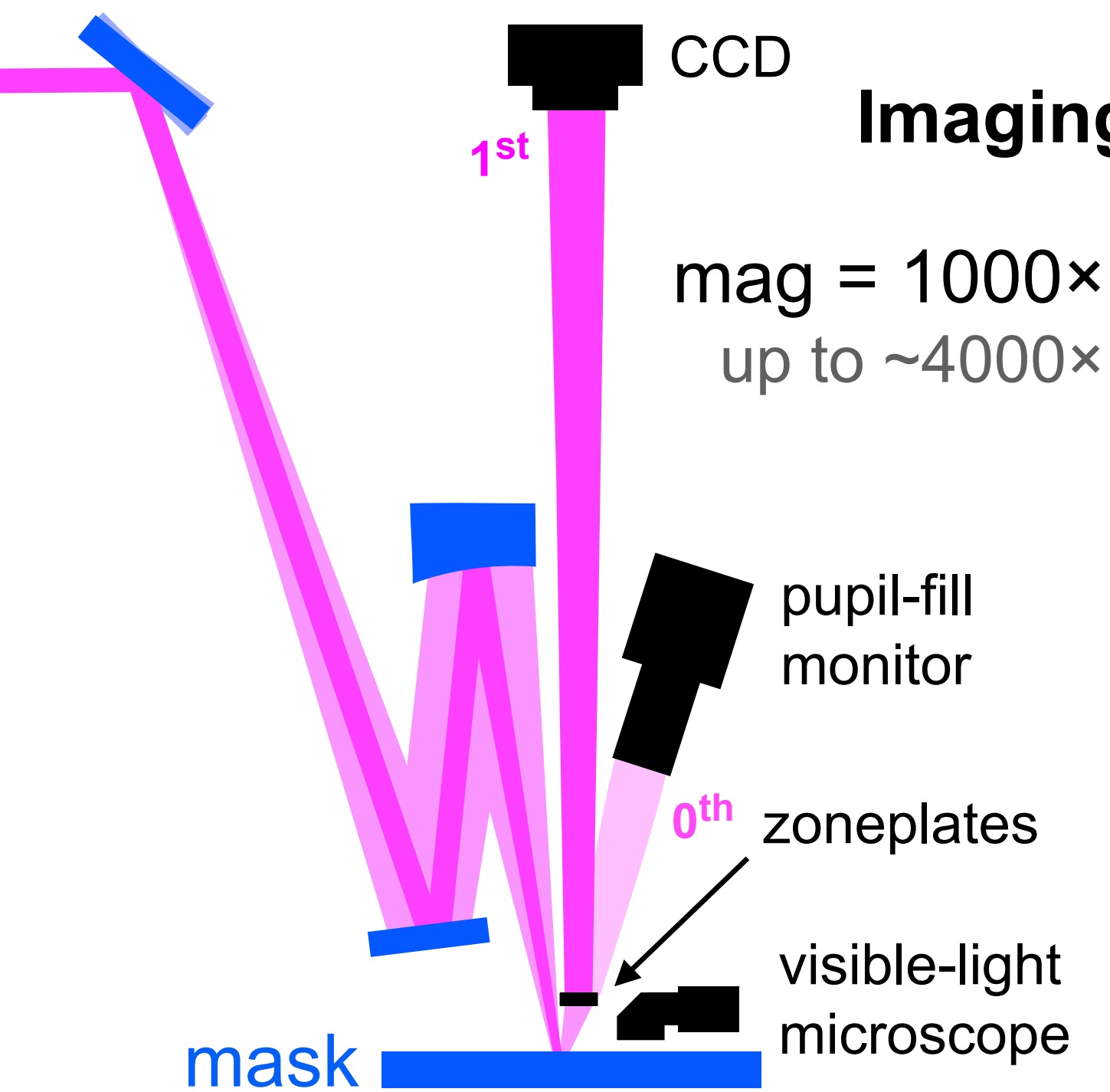


angle-scanner

condenser

mask

Imaging System



CCD

1st

mag = 1000x
up to ~4000x

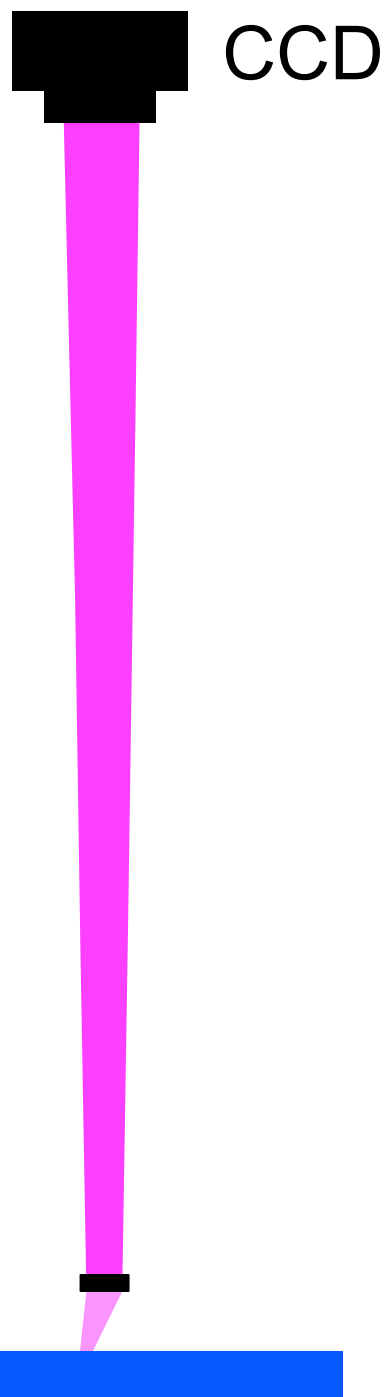
pupil-fill
monitor

0th
zoneplates

visible-light
microscope

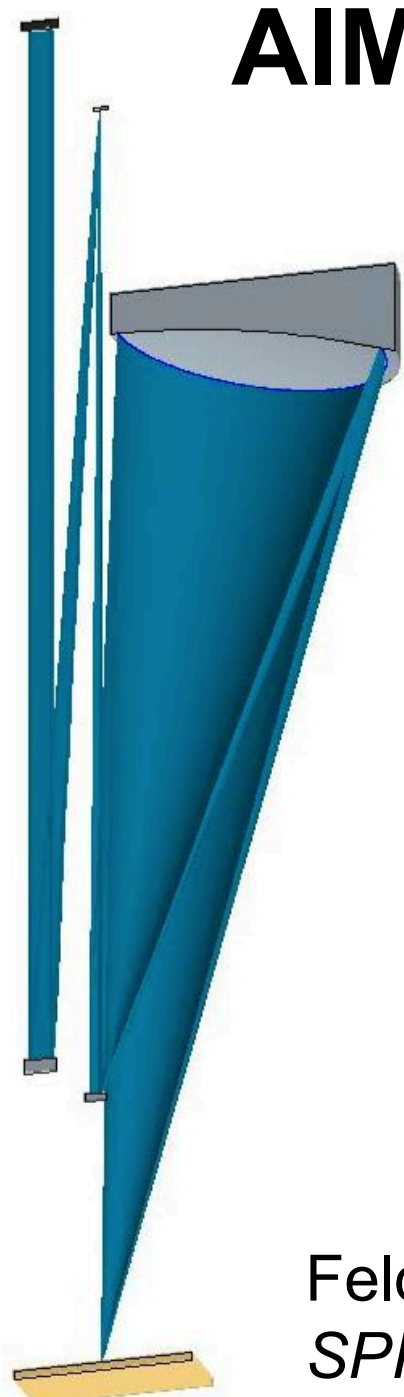
mask

AIT5
SEMATECH
& LBNL



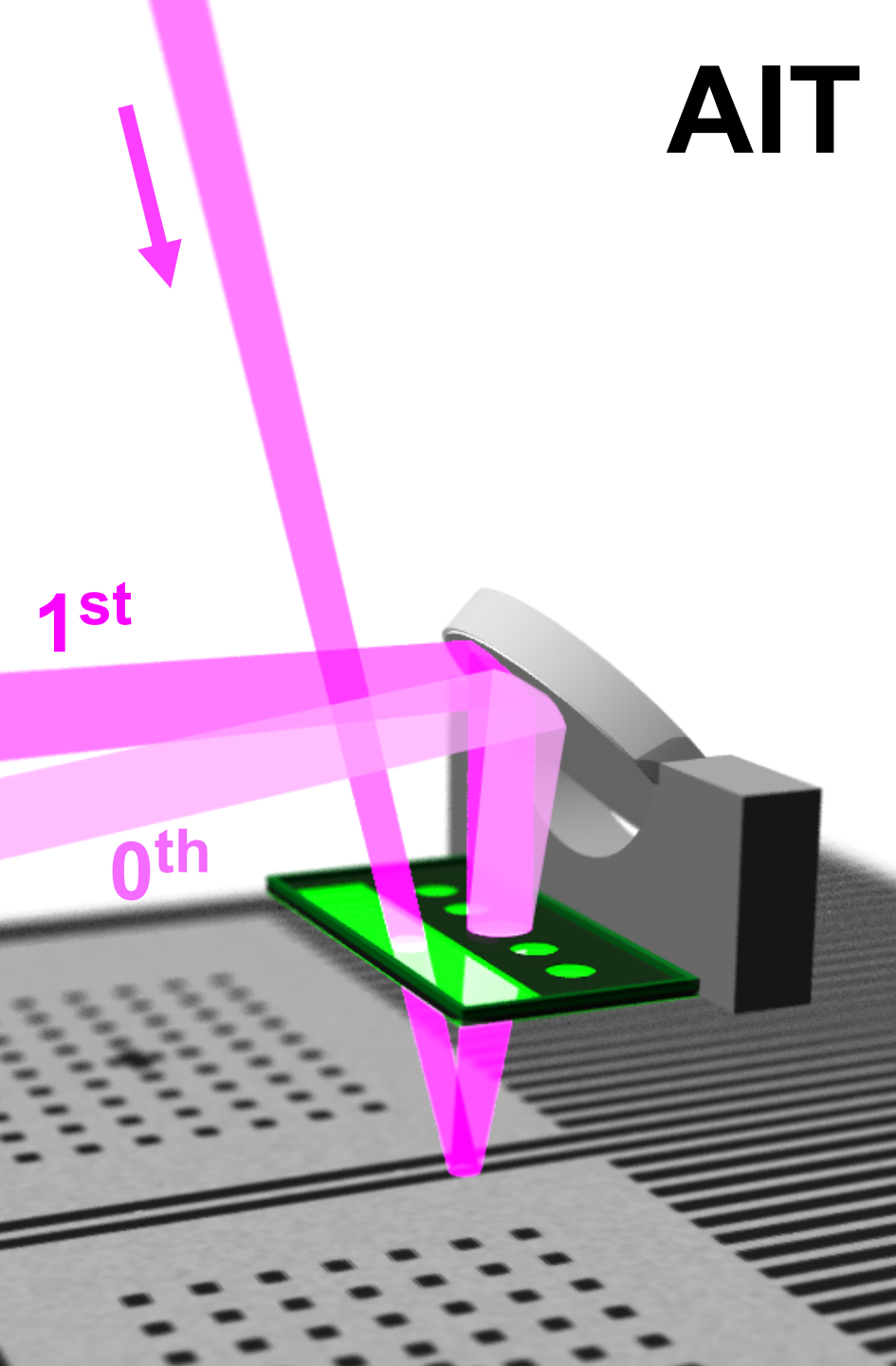
Goldberg, *SPIE*
7969 (2011)

AIMS™ EUV
Zeiss

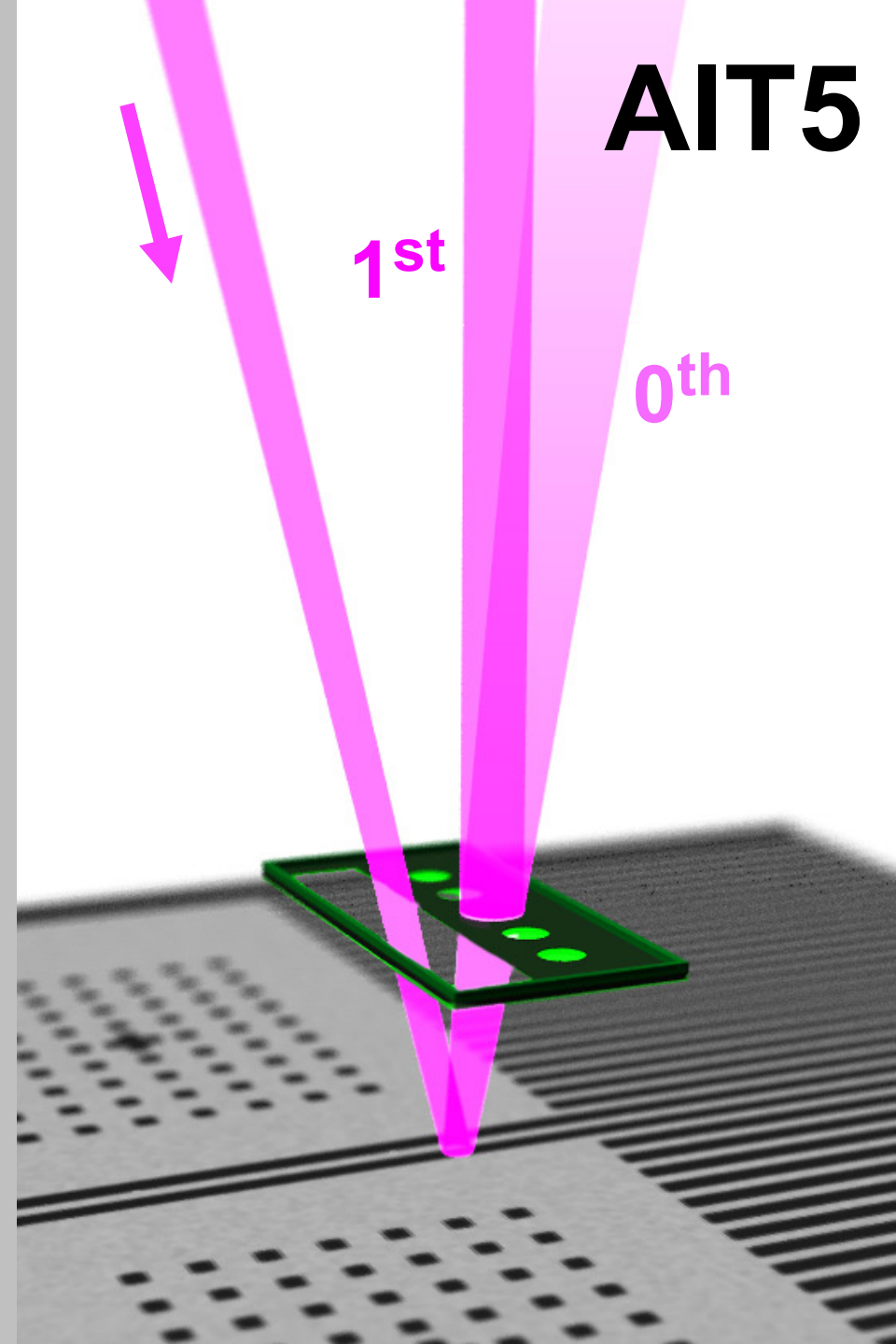


Feldmann,
SPIE **7636** (2010)

AIT



AIT5



Zoneplate objective lenses arrayed by NA

6°

8°

10°

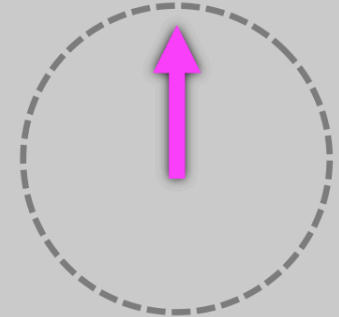
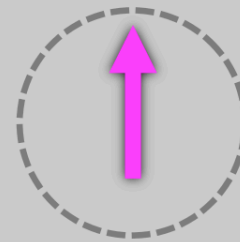
4xNA: 0.25

0.30

0.35

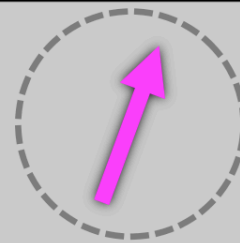
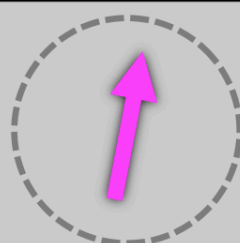
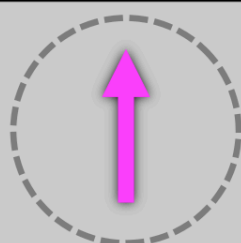
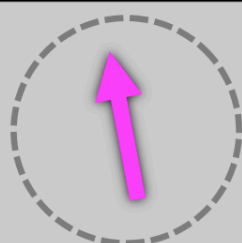
0.45

0.625

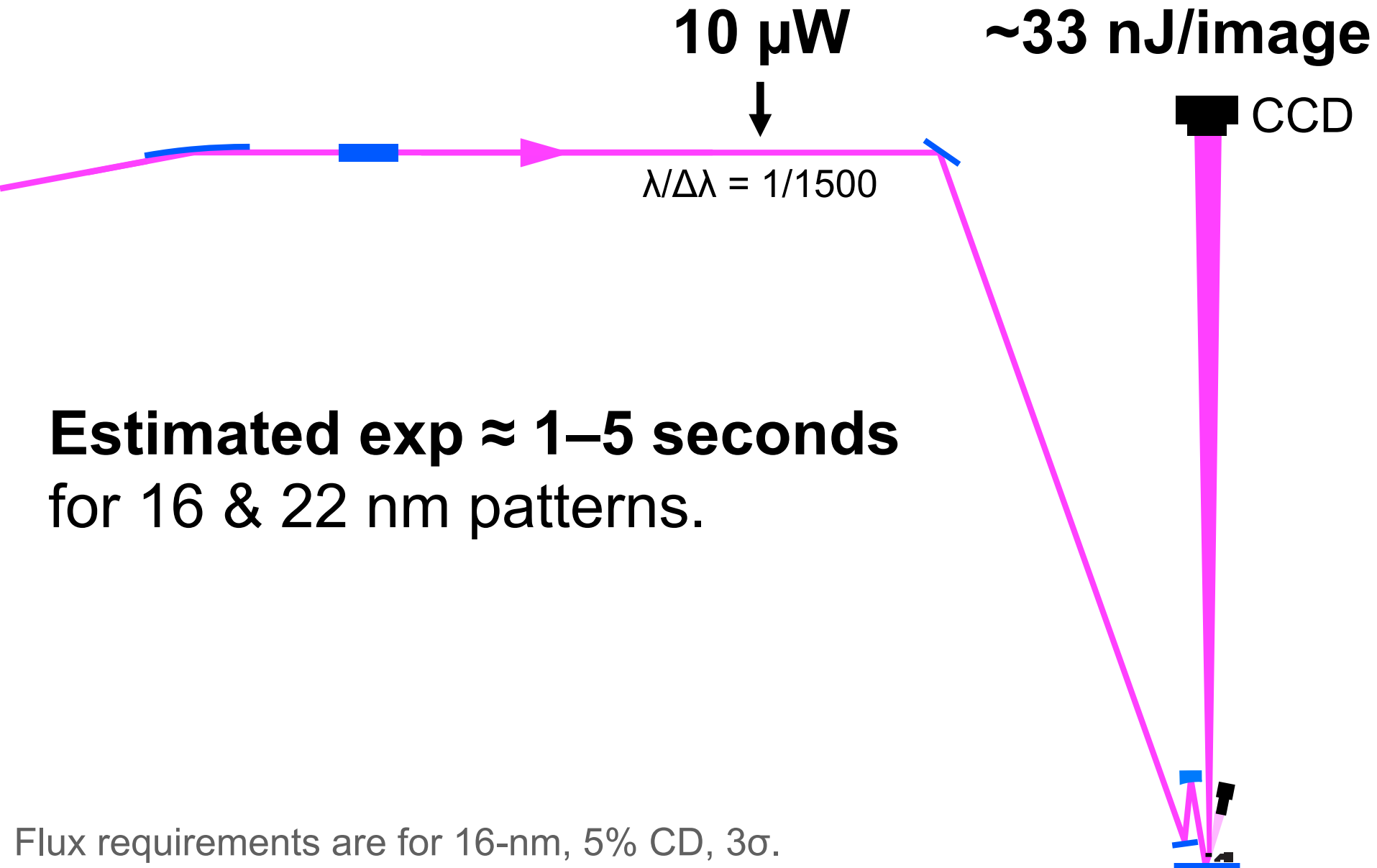


Zoneplate objective lenses arrayed by azimuthal angle

Φ : -25° -12.5° 0° 12.5° 25°



What about *power*?



Estimated exp \approx 1–5 seconds
for 16 & 22 nm patterns.

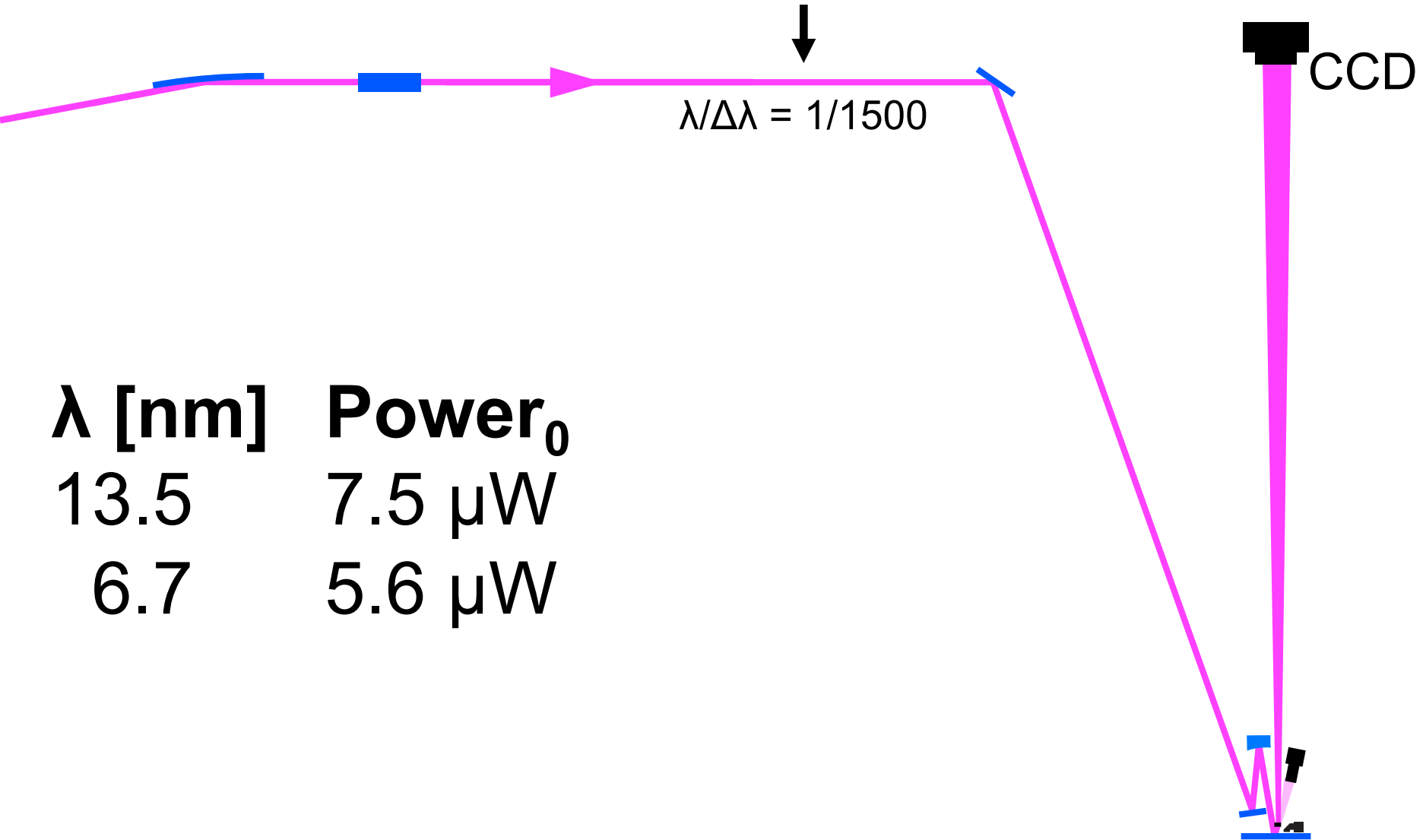
Flux requirements are for 16-nm, 5% CD, 3σ .
Wintz, *SPIE 7636* (2010).

AIT

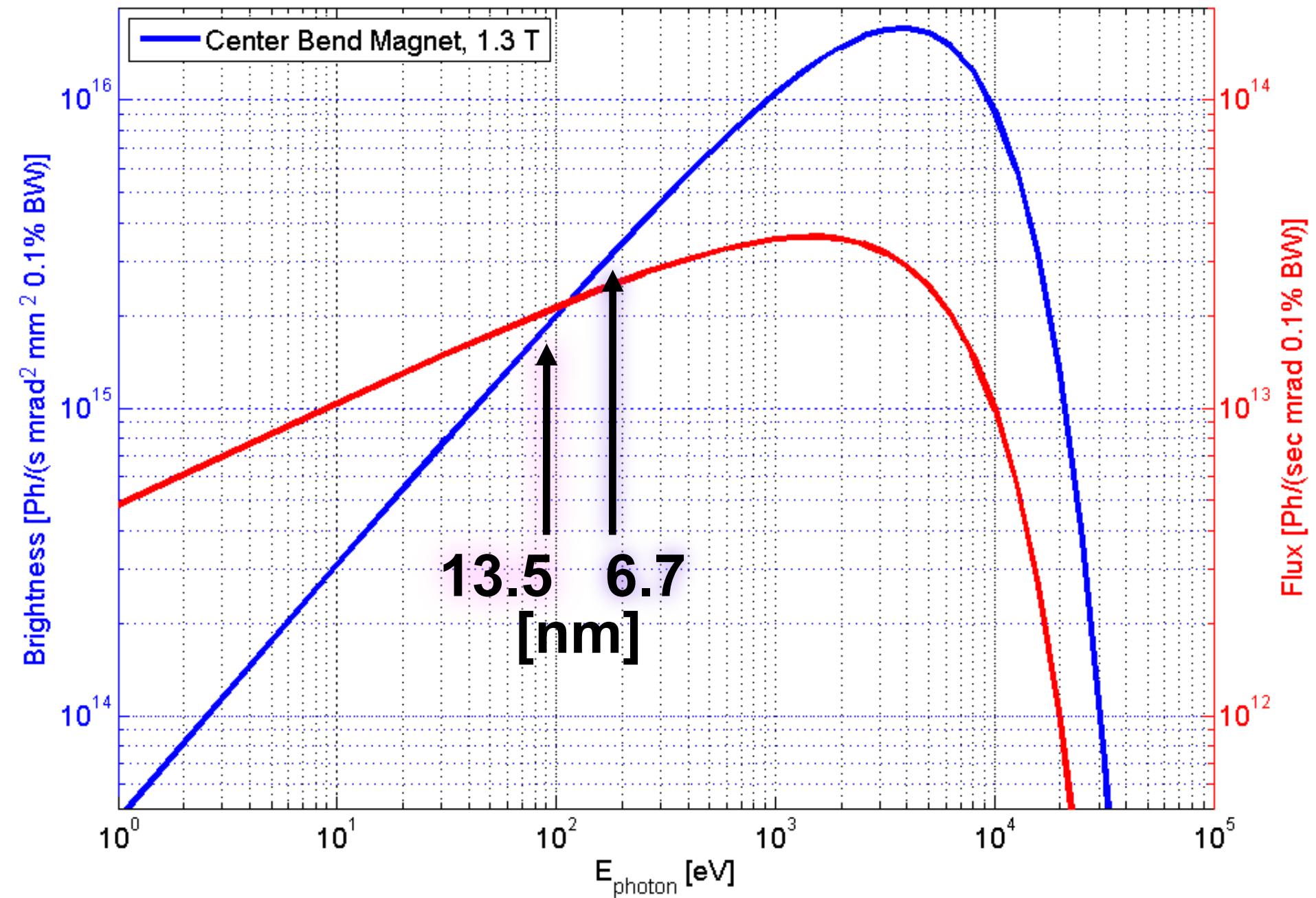
AIT5

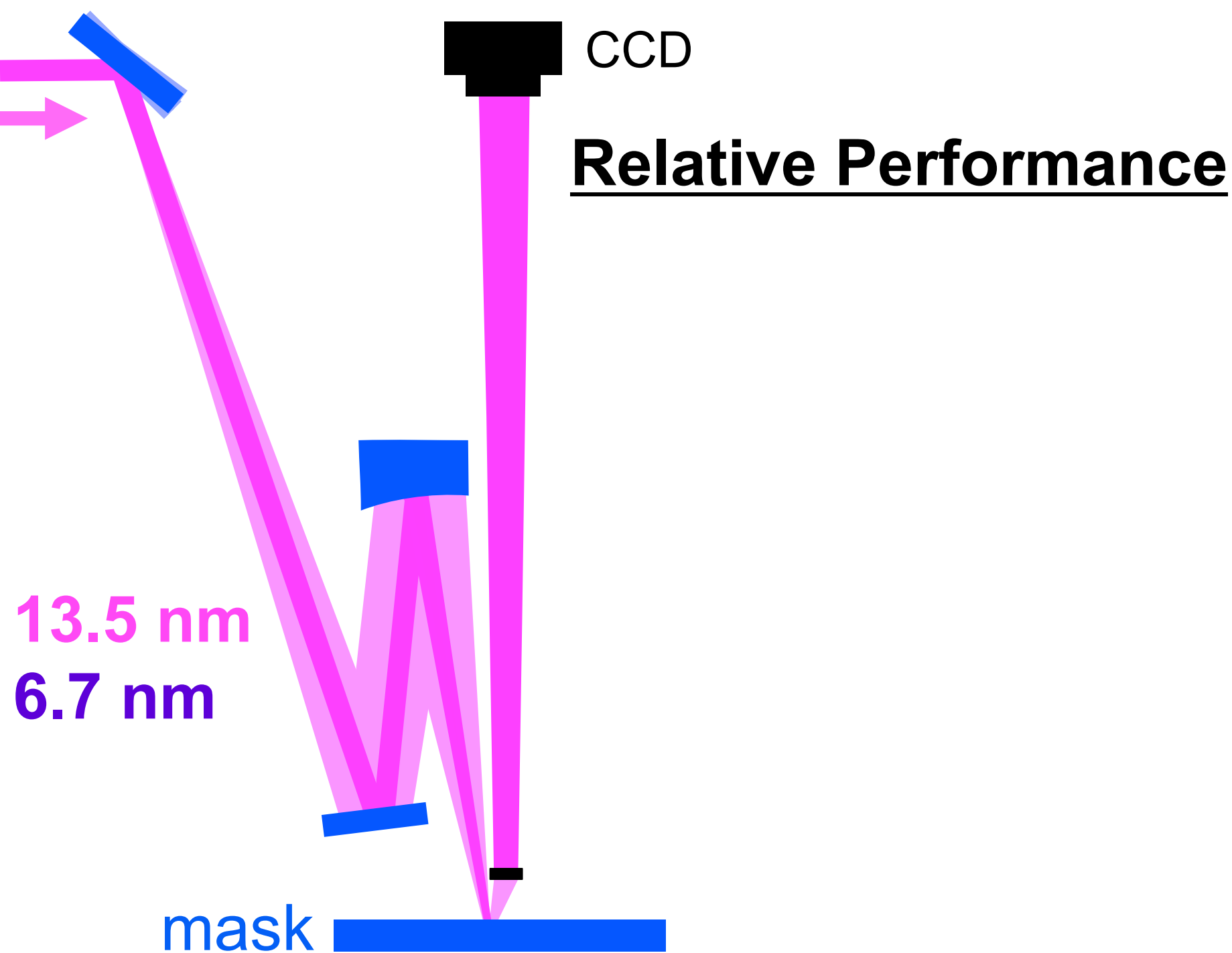
AIT 6.7?

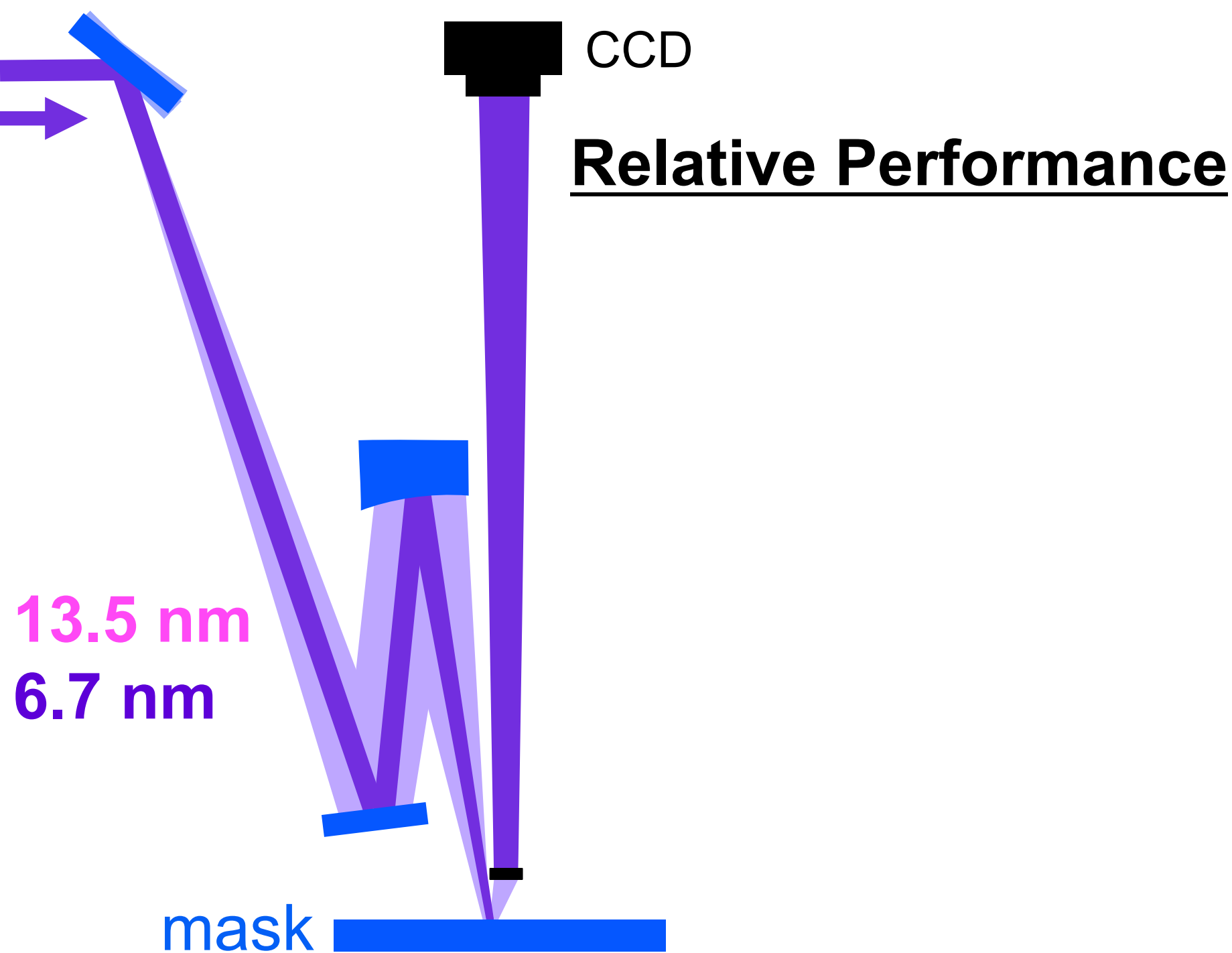
Beamline Power @ ALS

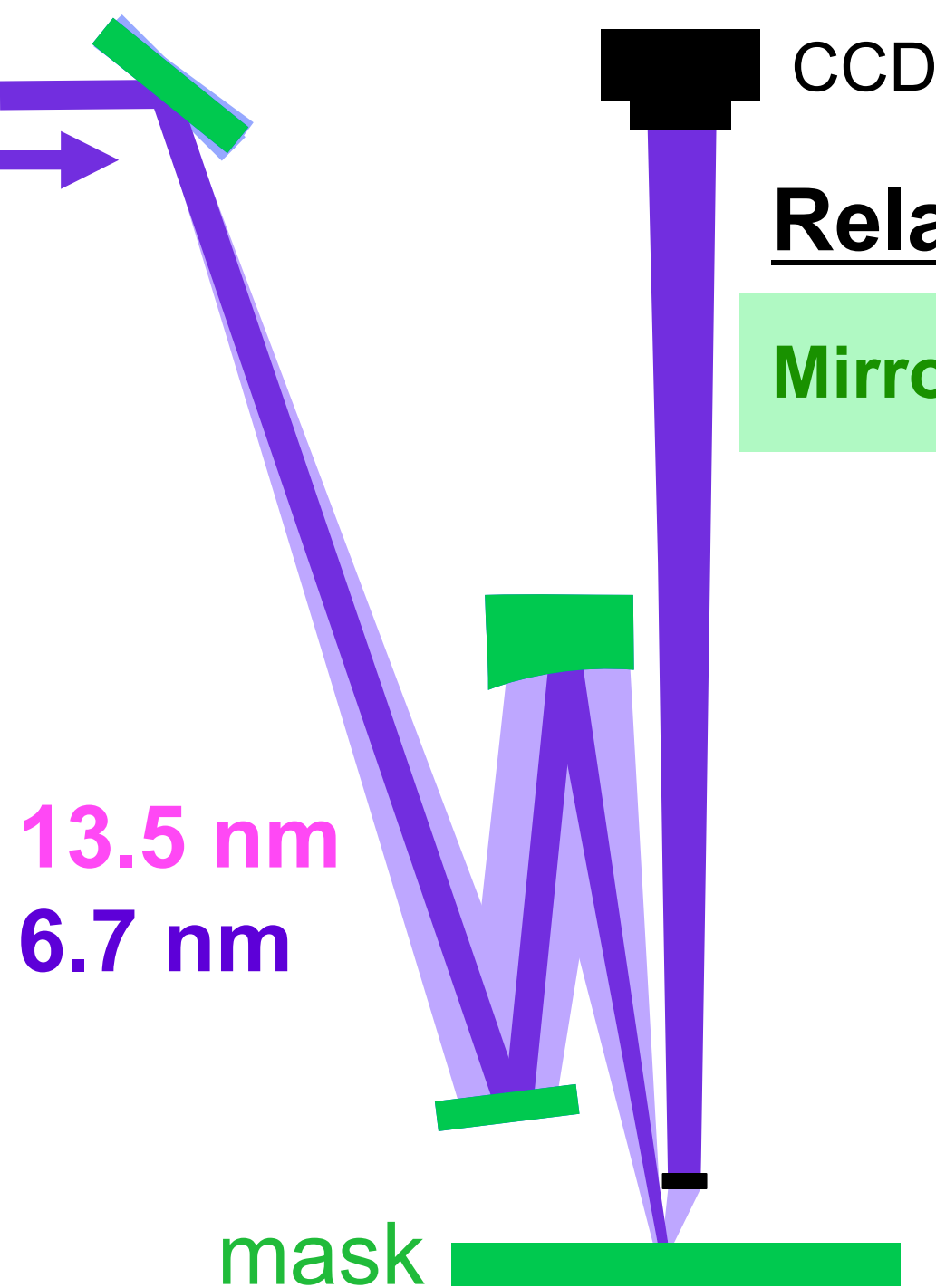


Advanced Light Source (ALS) @ LBNL









CCD

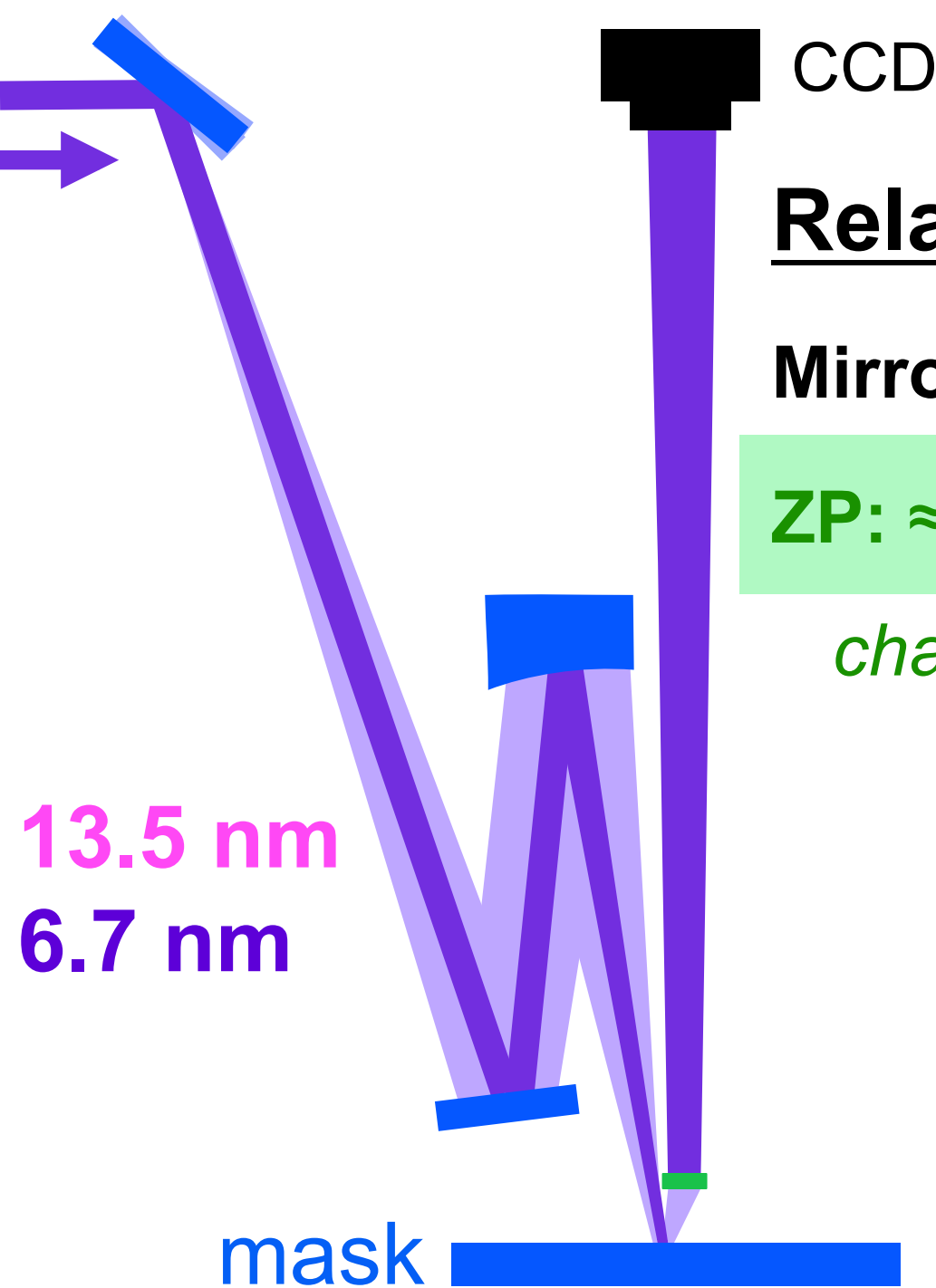
Relative Performance

Mirrors: $(0.45 / 0.65)^4 \approx 0.25$

13.5 nm

6.7 nm

mask

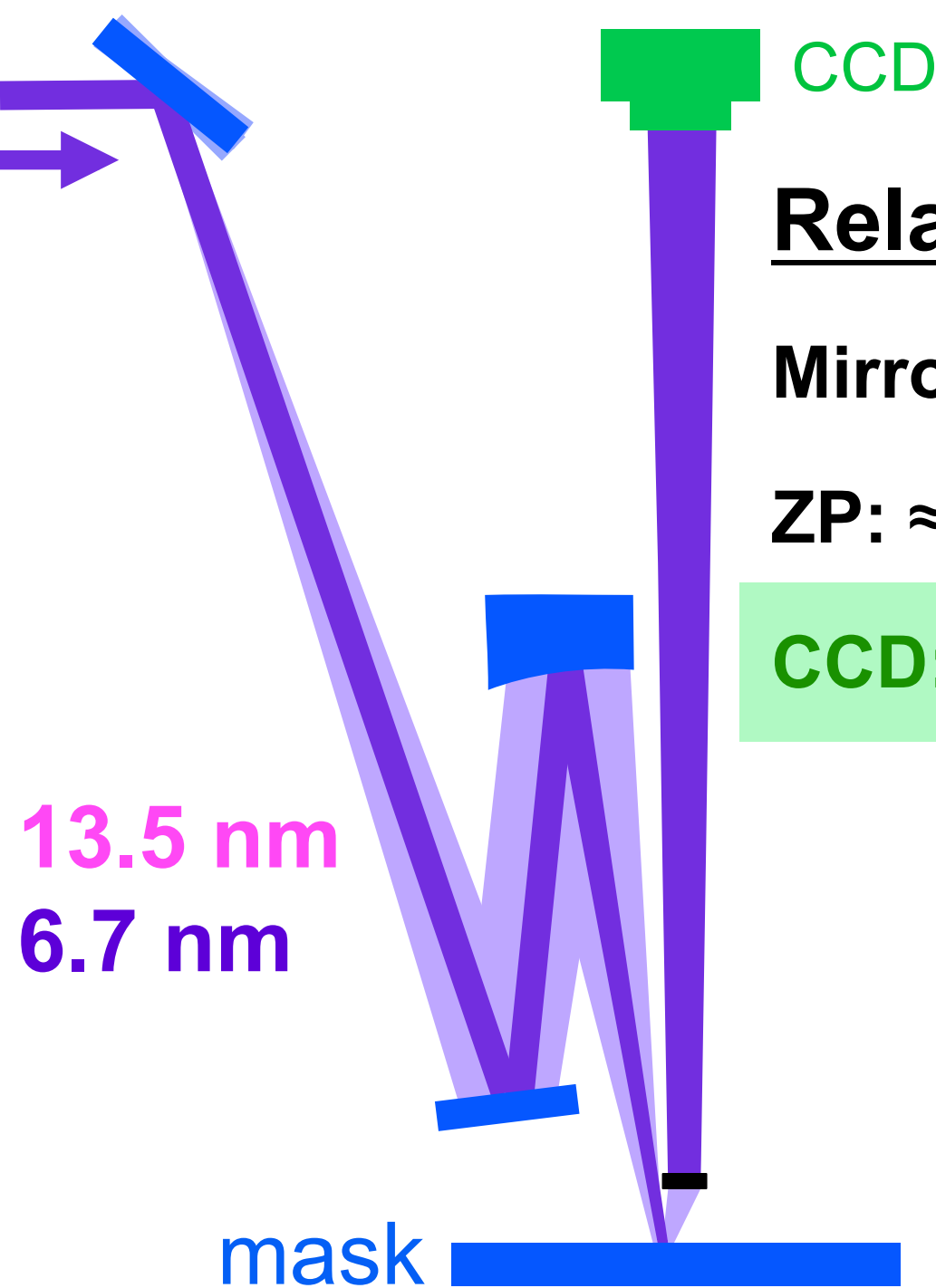


Relative Performance

Mirrors: $(0.45 / 0.65)^4 \approx 0.25$

ZP: ≈ 0.5 (bandwidth / 2)*

challenging at high-NA



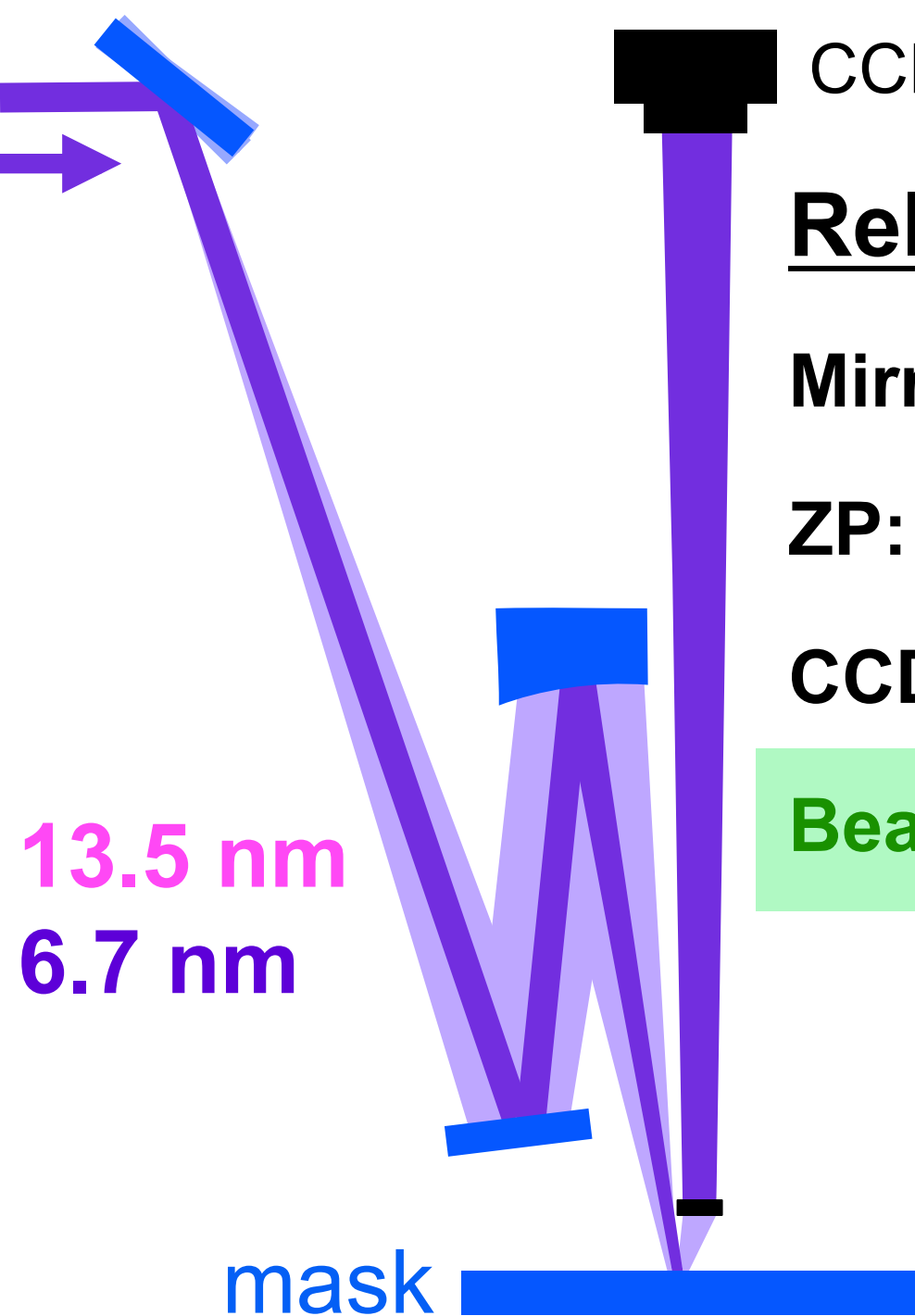
CCD

Relative Performance

Mirrors: $(0.45 / 0.65)^4 \approx 0.25$

ZP: ≈ 0.5 (bandwidth / 2)

CCD: ≈ 0.8 (detection)



CCD

Relative Performance

Mirrors: $(0.45 / 0.65)^4 \approx 0.25$

ZP: ≈ 0.5 (bandwidth / 2)

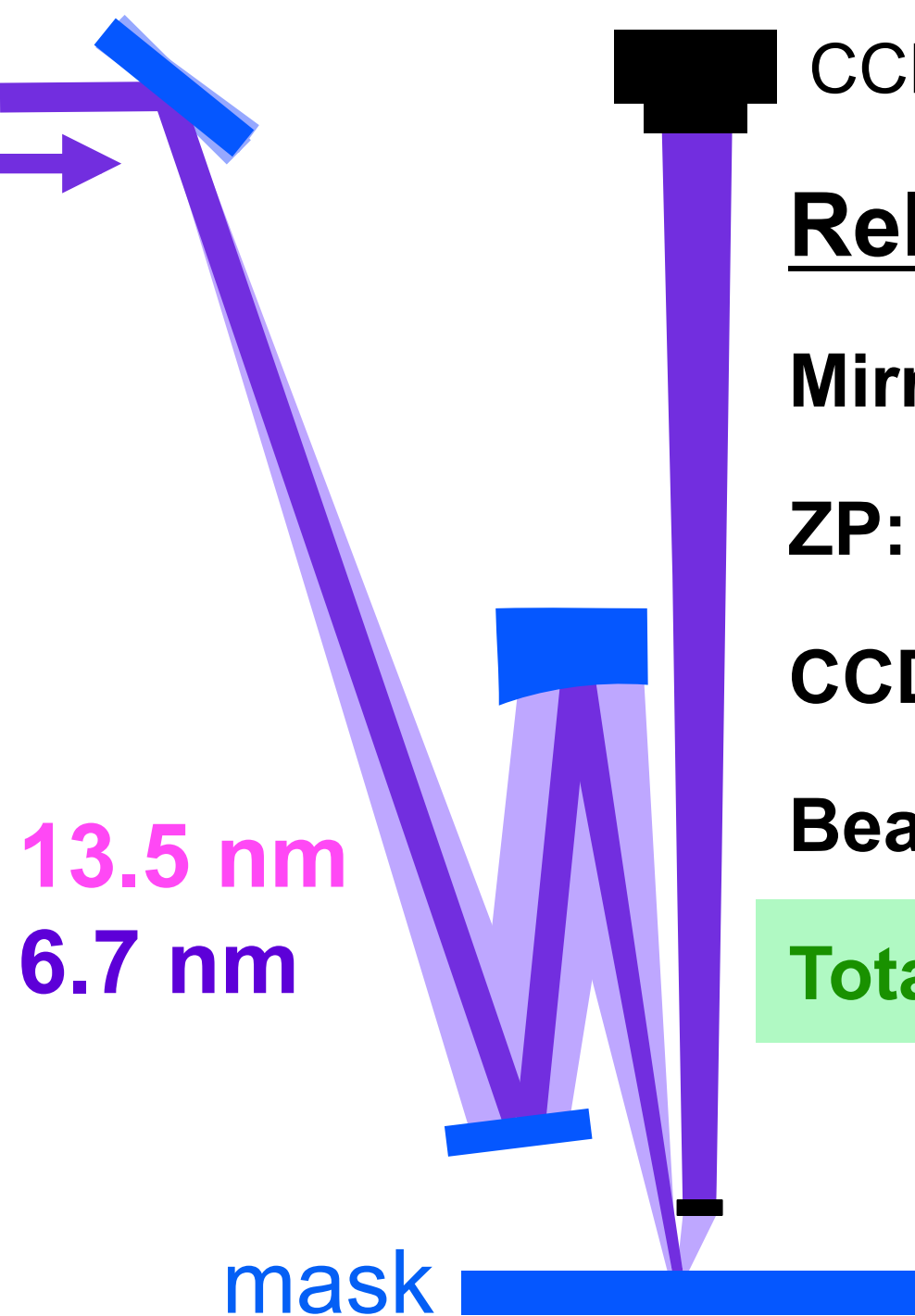
CCD: ≈ 0.8 (detection)

Beamline: ≈ 5.6 (power)

13.5 nm

6.7 nm

mask



Relative Performance

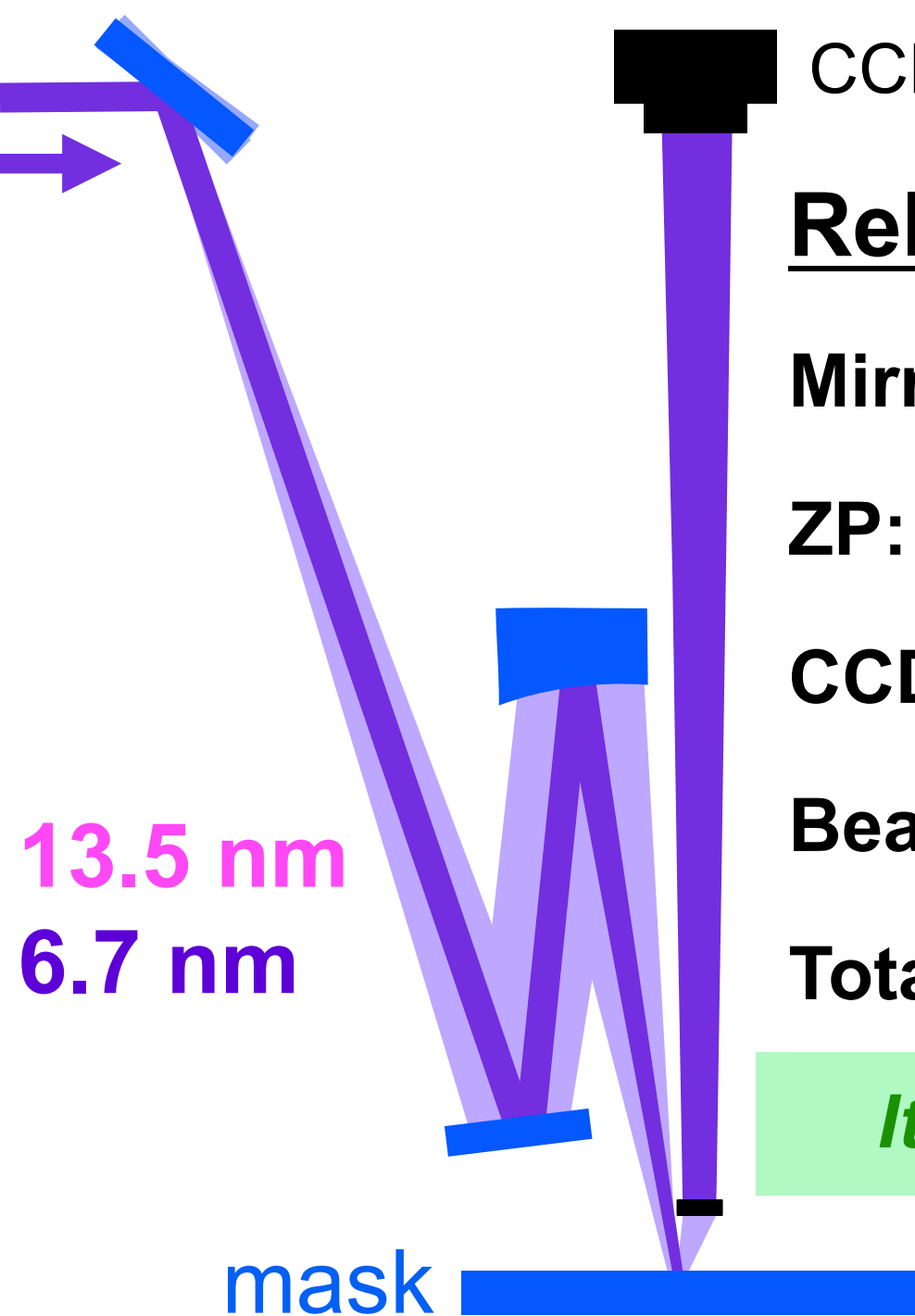
Mirrors: $(0.45 / 0.65)^4 \approx 0.25$

ZP: ≈ 0.5 (bandwidth / 2)

CCD: ≈ 0.8 (detection)

Beamline: ≈ 5.6 (power)

Total: $\approx 1/2$ power $\approx 1/4$ ph



Relative Performance

Mirrors: $(0.45 / 0.65)^4 \approx 0.25$

ZP: ≈ 0.5 (bandwidth / 2)

CCD: ≈ 0.8 (detection)

Beamline: ≈ 5.6 (power)

Total: $\approx 1/2$ power $\approx 1/4$ ph

It will work at 6.7 nm!

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> 16 nm

low σ

$\angle 6^\circ$

AIT5

> 6 nm

any σ

up to $\angle 10^\circ$

AIT5

> 6 nm

any σ

up to $\angle 10^\circ$

AIT6.7

> ? nm

any σ

up to $\angle 10^\circ$

The AIT team



Iacopo Mochi
Project Scientist



James Macdougall
Graduate Student



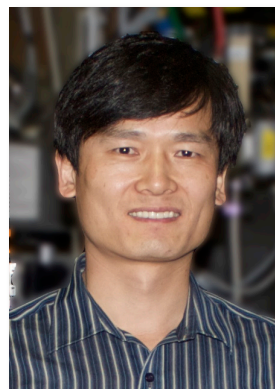
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Bryan Rice
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